

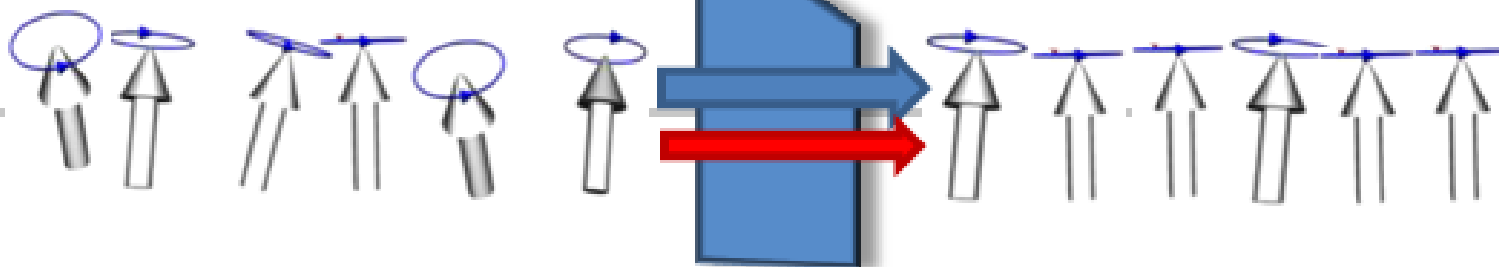
Magneto-Seebeck effect in magnetic tunnel junctions

Jakob Walowski, Andreas Mann, Marvin Walter, Valdislav Zbarsky, Anissa Zeghuzi,
Markus Münzenberg, *I. Physikalisches Institut, Universität Göttingen, Germany*

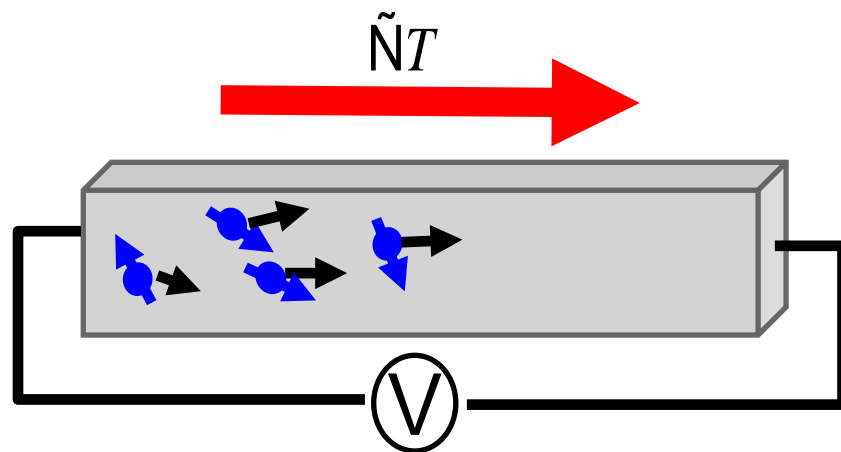
Michael Czerner, Michael Bachmann, Christian Heiliger, *I. Physikalisches Institut,
Justus-Liebig-Universität Gießen*

J.S. Moodera, *MIT Cambridge, USA*

Markus Schäfers, Daniel Ebke, Günter Reiss, Andy Thomas*,
Department of Physics, Universität Bielefeld, Germany
*Department of Physics, * Institut für angewandte Physik, Hamburg, Germany*

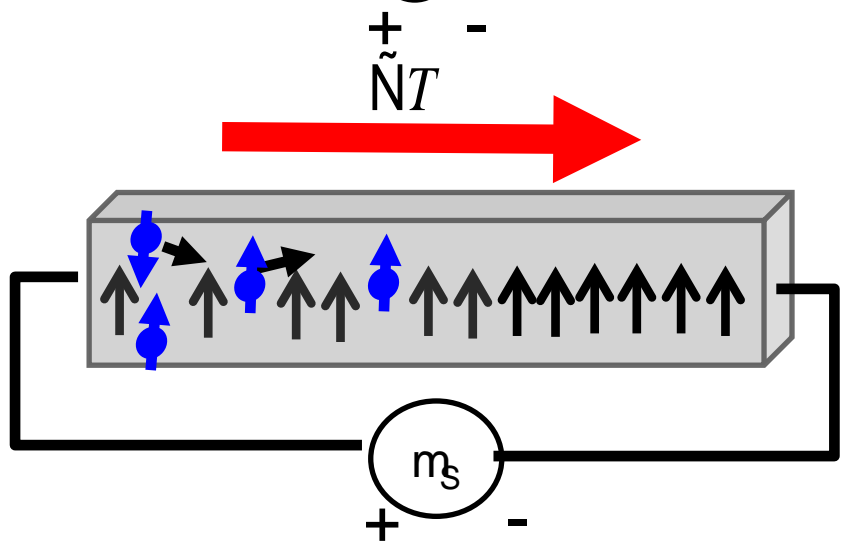


Charge and spin-dependent Seebeck effect



$$DV = S_D T$$

„charge
accumulation“



$$Dm_s = S_S T$$

„spin
accumulation“

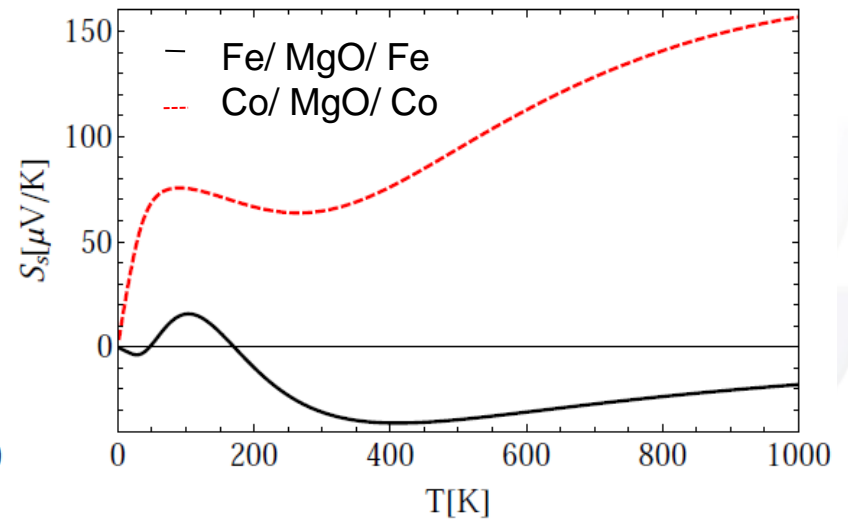
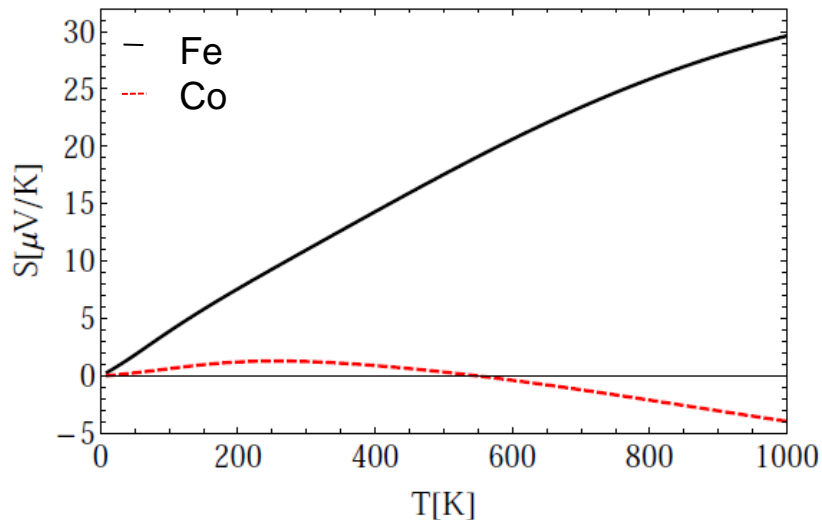
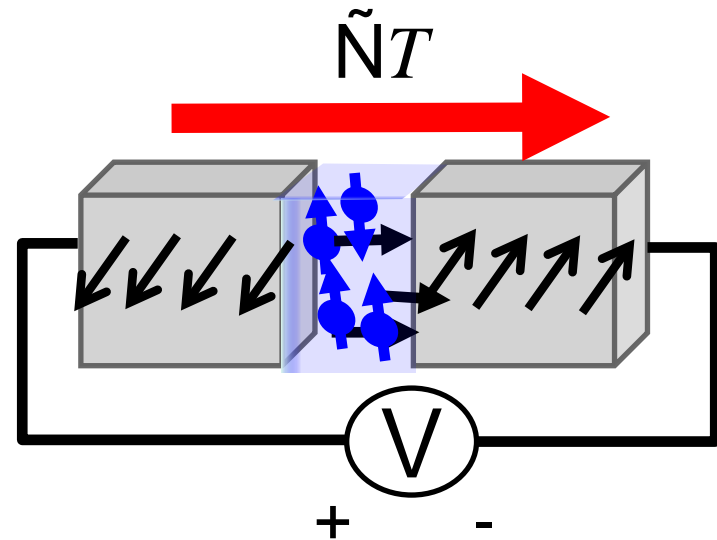
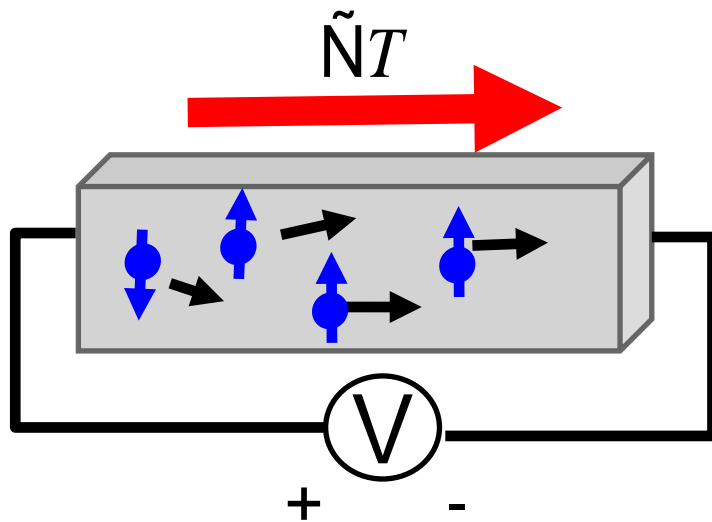
Theory: M. Johnson and R. H. Silsbee, Phys. Rev. B 35, 4959 (1987).

Experiment: L. Gravier Phys. Rev. B 73, 024419 (2006).
K. Uchida Nature 455, 778 (2008).

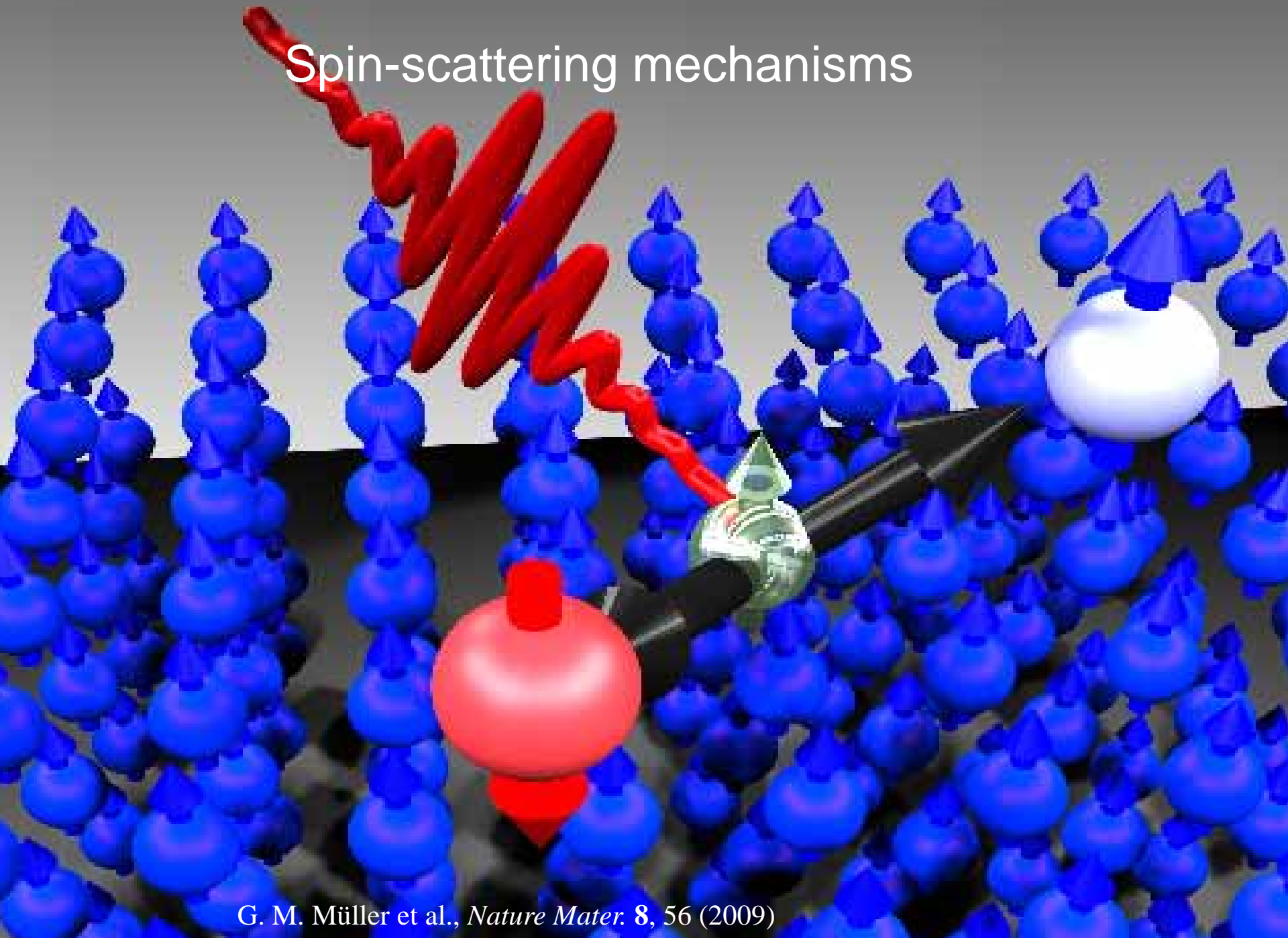
A. Slachter Nature Phys. 6, 879 (2010).

G.E.W. Bauer, Spin Caloritronics, Solid State Comm. 150, 459 (2010).

... in bulk and tunnel junctions

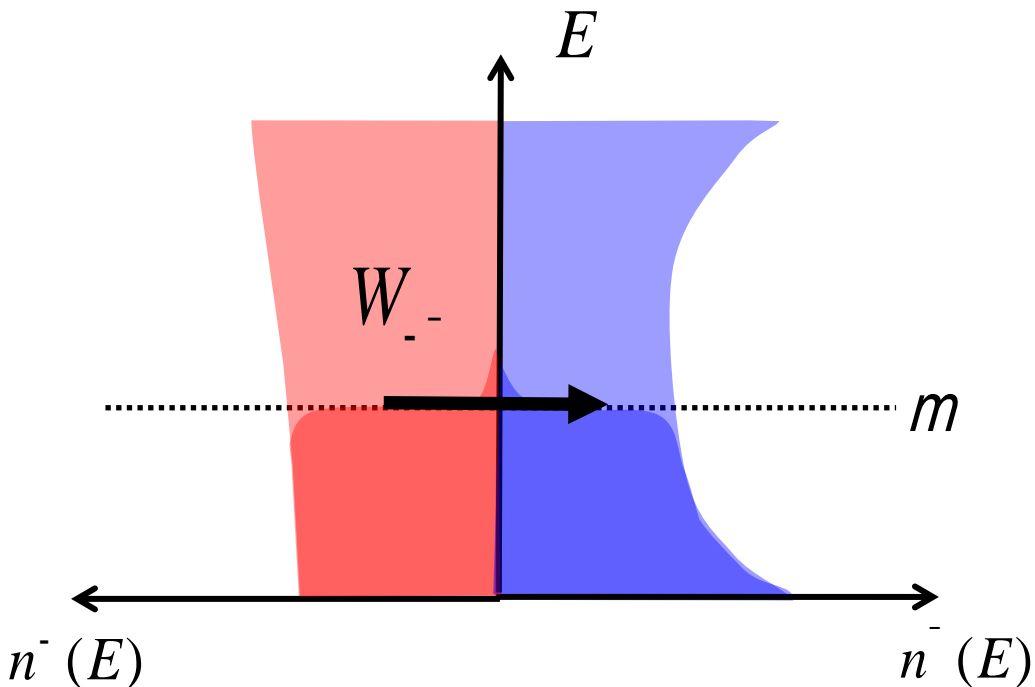


Spin-scattering mechanisms



Spin-scattering mechanisms

Elliott-Yafet process: femtosecond demagnetization and FMR



$$W_{-} \sim n_{e}^{-}(E_F) c^2 n_{h}^{-}(E_F)$$

Spin mixing:

$$c \sim V_{SO} / \Delta E_{exch} \quad \text{Spin-orbit interaction}$$

Spin polarization:

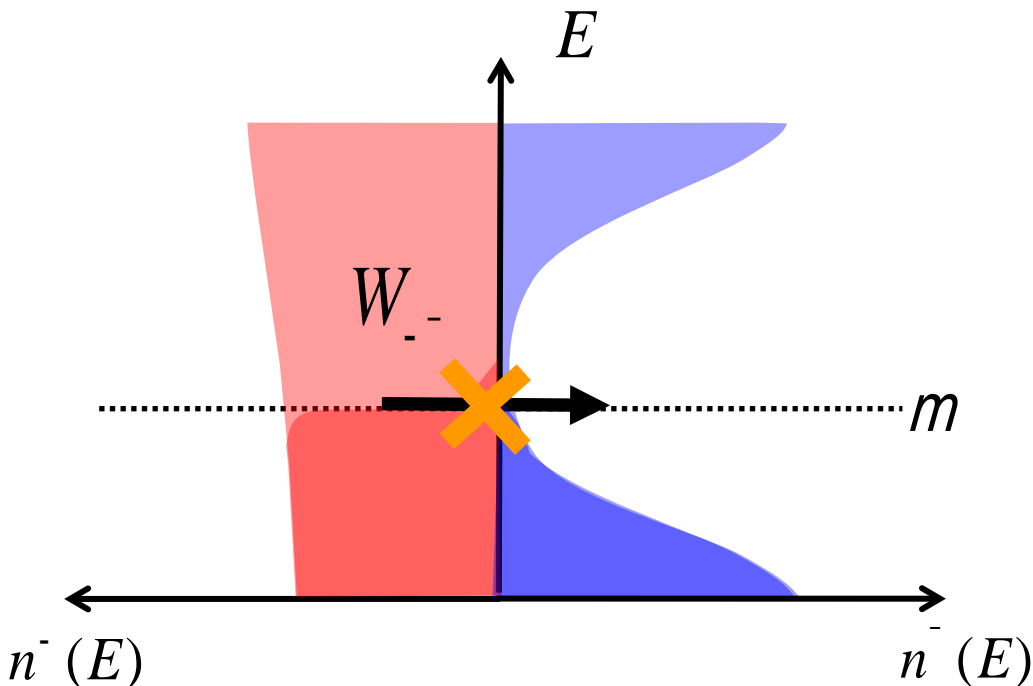
$$P_0 = \frac{n_{e}^{-} - n_{e}^{+}}{n_{e}^{-} + n_{e}^{+}}$$

R. J. Elliott, *Phys. Rev.* **96** (1954).

Fs pump-probe: G. M. Müller et al., *Nature Mater.* **8**, 56 (2009)

Spin-scattering mechanisms

Elliott-Yafet process: femtosecond demagnetization and FMR



$$W_{-} \sim n_{e}^{-}(E_F) c^2 n_{h}^{-}(E_F)$$

Spin mixing:

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Spin polarization P dependent relaxation

$$P_0 = \frac{n_{e}^{-} - n_{e}^{+}}{n_{e}^{-} + n_{e}^{+}}$$

For $P \ll 1$:

- Spin-flip processes are prohibited
- Electron and spin system are isolated

R. J. Elliott, *Phys. Rev.* **96** (1954).

Fs pump-probe: G. M. Müller et al., *Nature Mater.* **8**, 56 (2009)

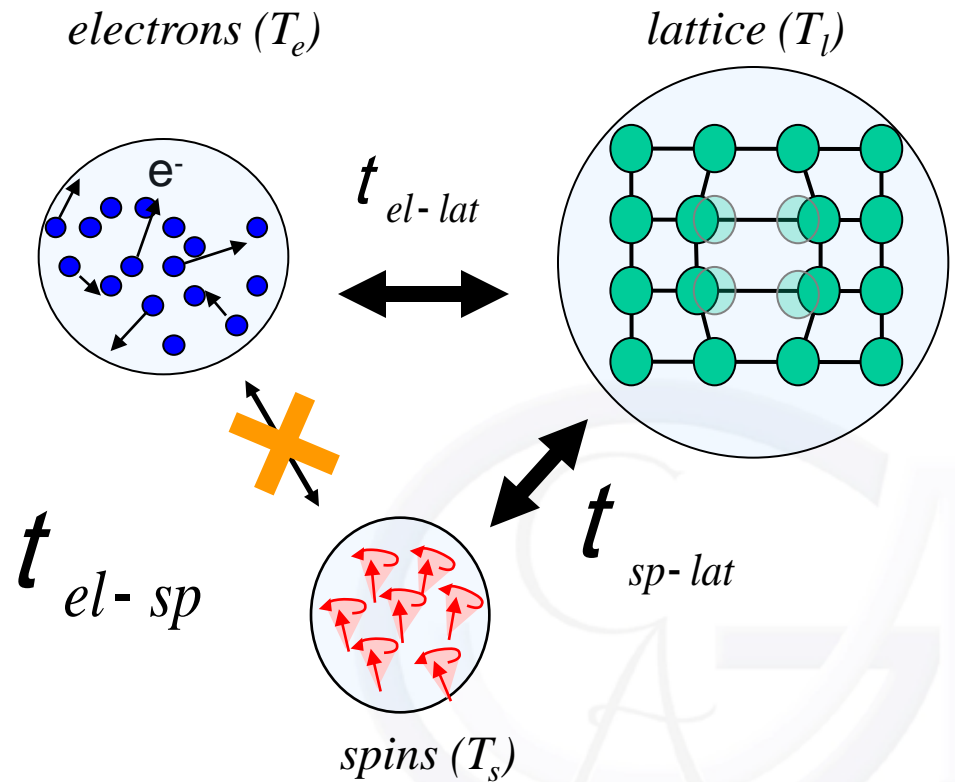
Spin-scattering mechanisms

Test of the effect of the coupling parameter:

- g_{el-sp}
- 2nd: suppression of the spin scattering

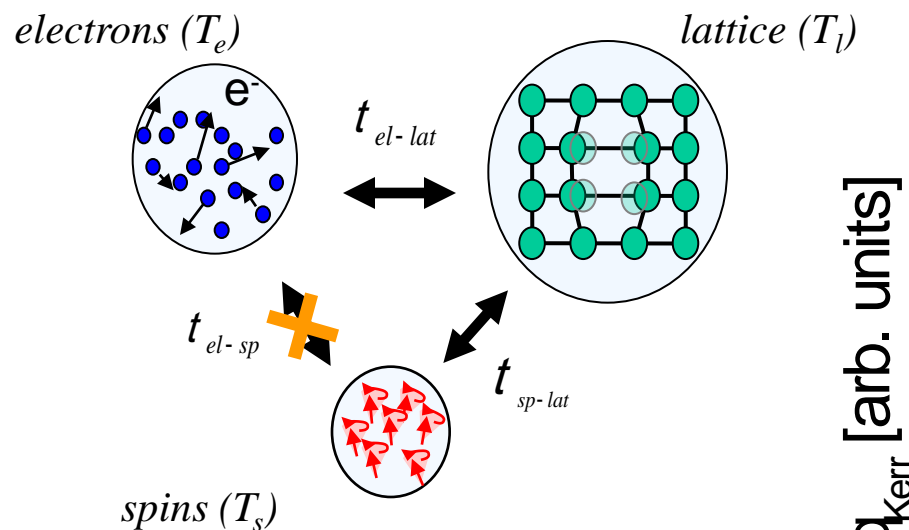
Coupling parameters

- $g_{el-lat} > g_{sp-lat} > g_{el-sp}$

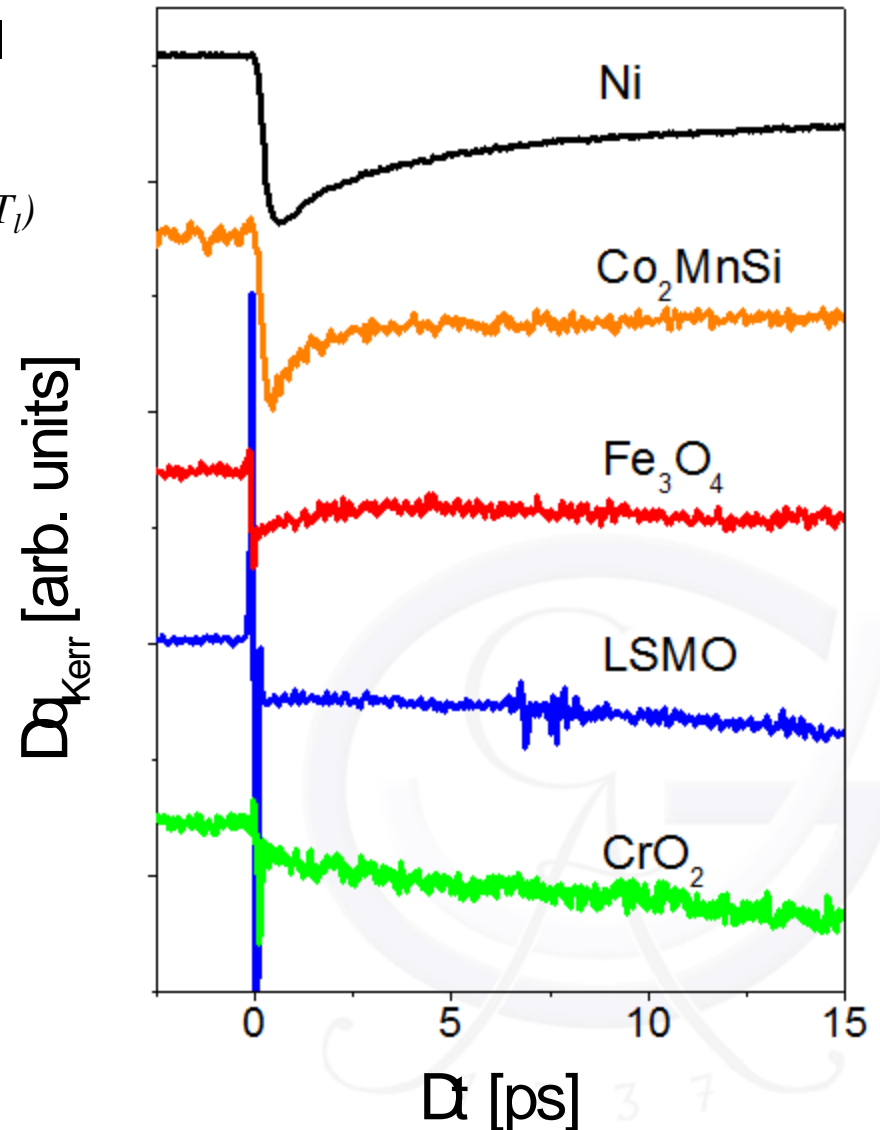


Spin relaxation in half metals

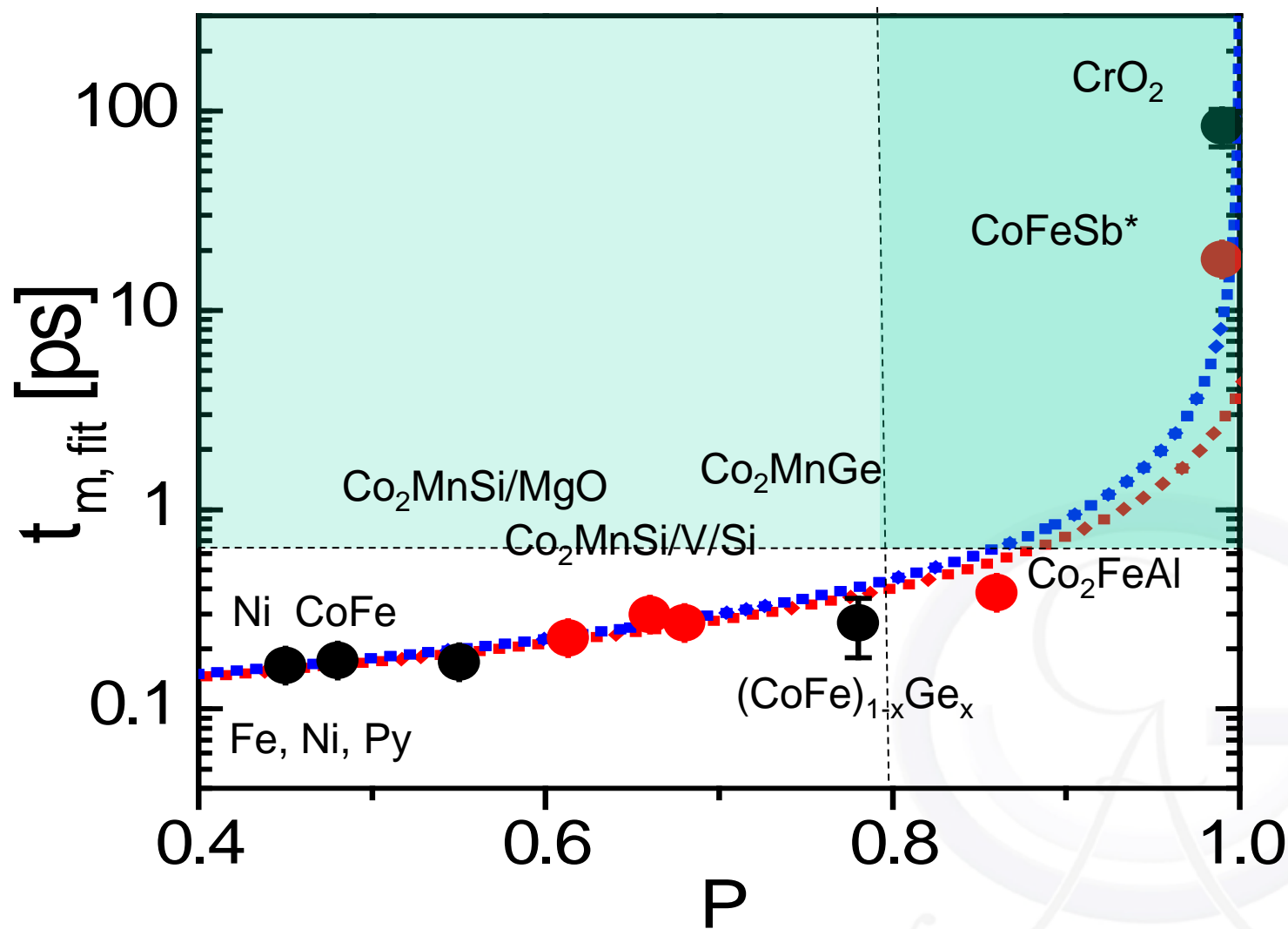
Three temperature model: half metal



- Spin-flip processes are prohibited
- Electron and spin system are isolated



Spin relaxation in half metals



Magneto-Seebeck effect?

- “Conventional” Seebeck effect: Voltage generation due to a temperature gradient in the material:

$$DV = SDT$$

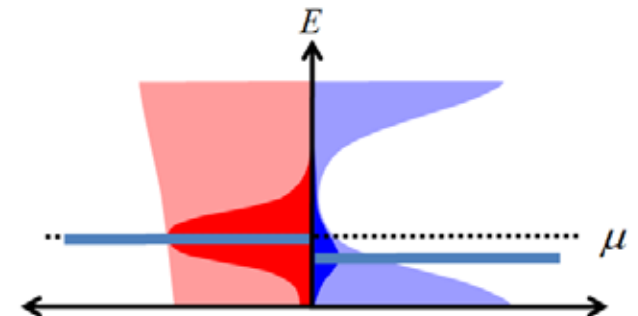
- In a magnetic tunnel junction dependence on magnetization orientation:

$$S_{\text{MS}} = \frac{S_{\text{P}} - S_{\text{AP}}}{\min(S_{\text{P}}, S_{\text{AP}})}$$

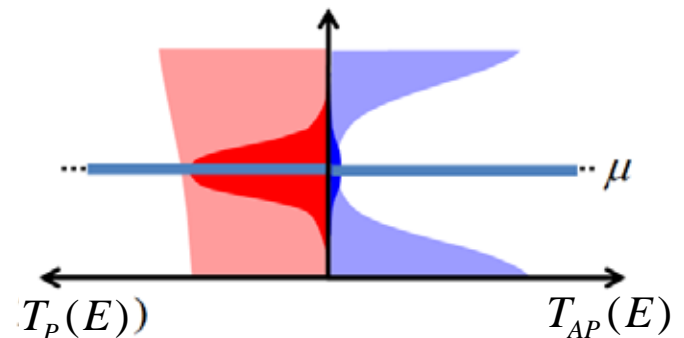
“Magneto-Seebeck effect”

Magnetic tunnel junction

High magneto-Seebeck effect



Low magneto-Seebeck effect



People who do the work



Benjamin Lenk



Jakob Walowski

Andreas Mann (now EPFL),
Henning Ulrichs (now U Münster),
Fabian Garbs

Bachelor students:

Martin Lüttich, Christian
Leutenantsmeyer, Jelena Panke,
Nils Abeling, Mirco Marahrens,
Anissa Zeghuzi



Marvin Walter

.... + Valdislav Zbarsky

Outline

- Introduction into coherent tunneling
- Magneto-Seebeck experiment:
 - Experimental setup
 - Simulations of the temperature gradients
- Ab initio calculations
 - Comparison to the experiment
- Summary



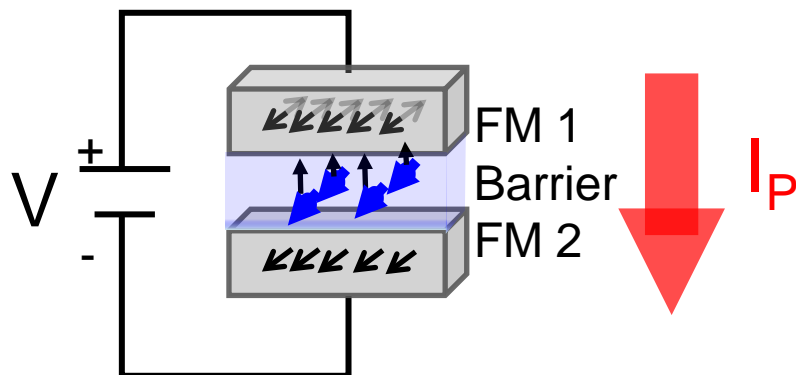
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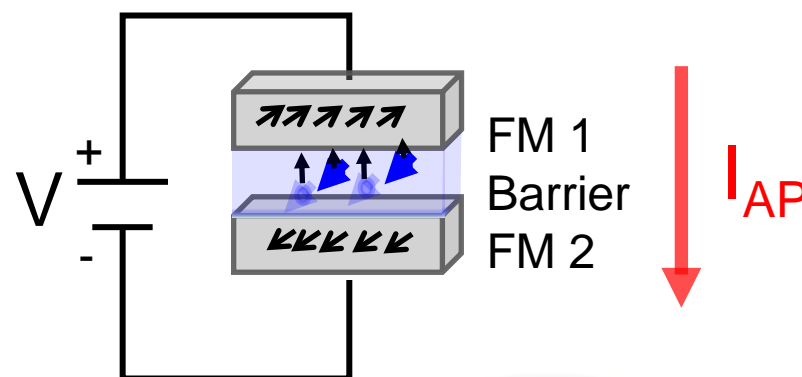


Giant tunneling magnetoresistance

Parallel magnetization



Antiparallel magnetization

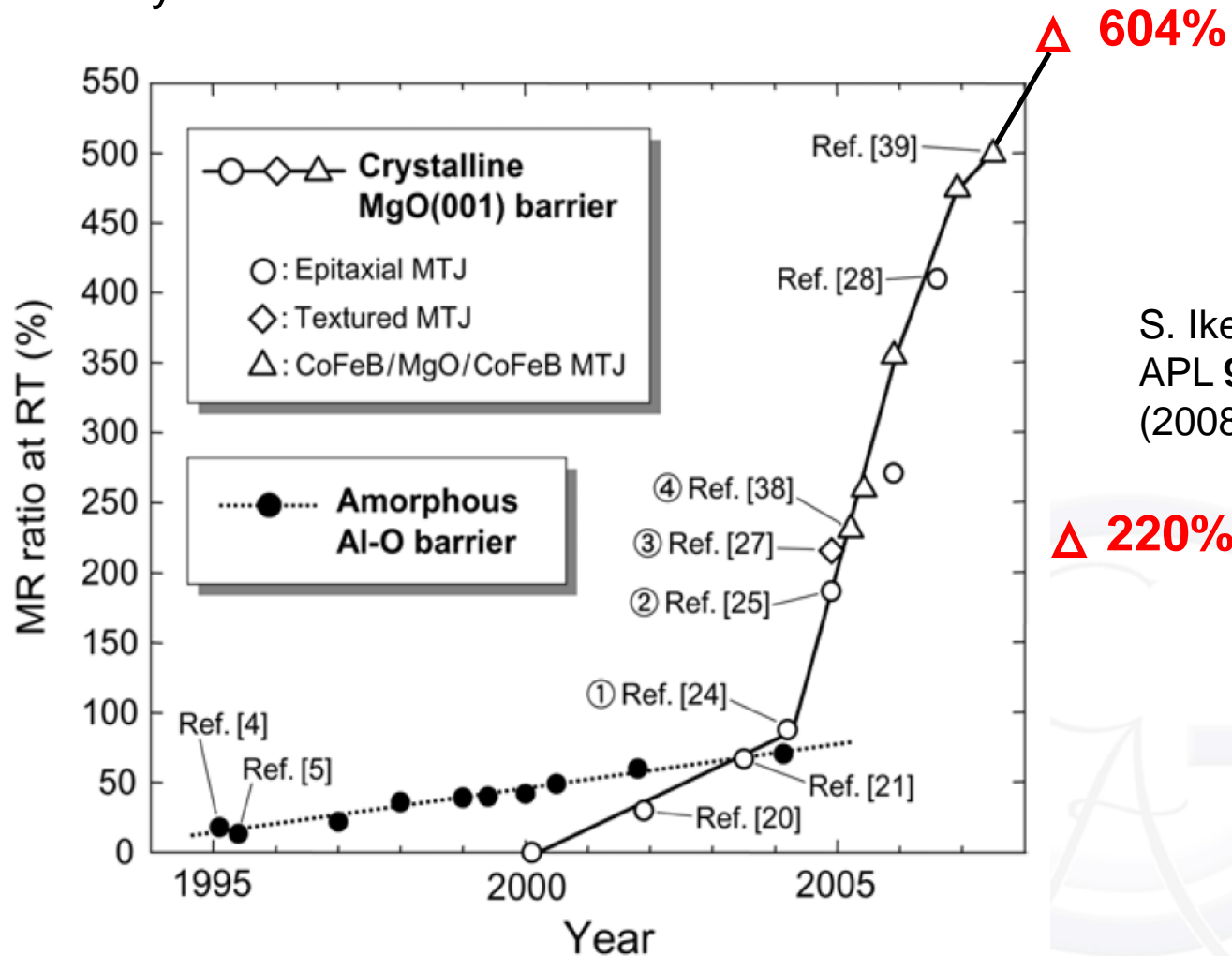


Resistance change is tunneling magnetoresistance (TMR):

$$\text{TMR} = \frac{R_{AP} - R_P}{R_P}$$

Giant tunneling magnetoresistance

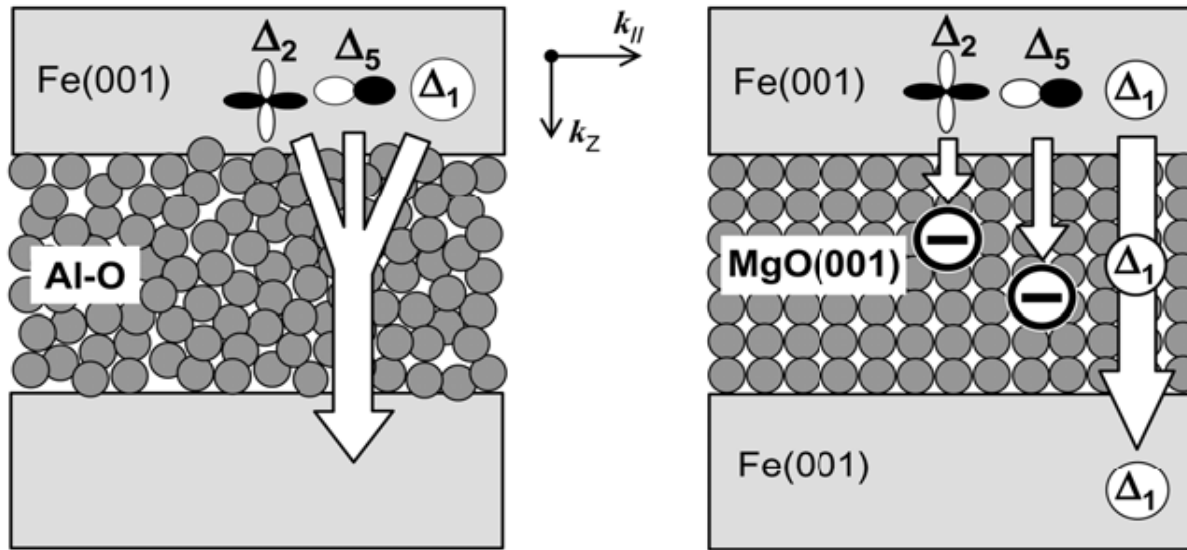
Experimentally achieved TMR



S. Ikeda et al.
APL **93**,082508
(2008)

Giant tunneling magnetoresistance

Difference between Al_2O_3 and MgO barriers

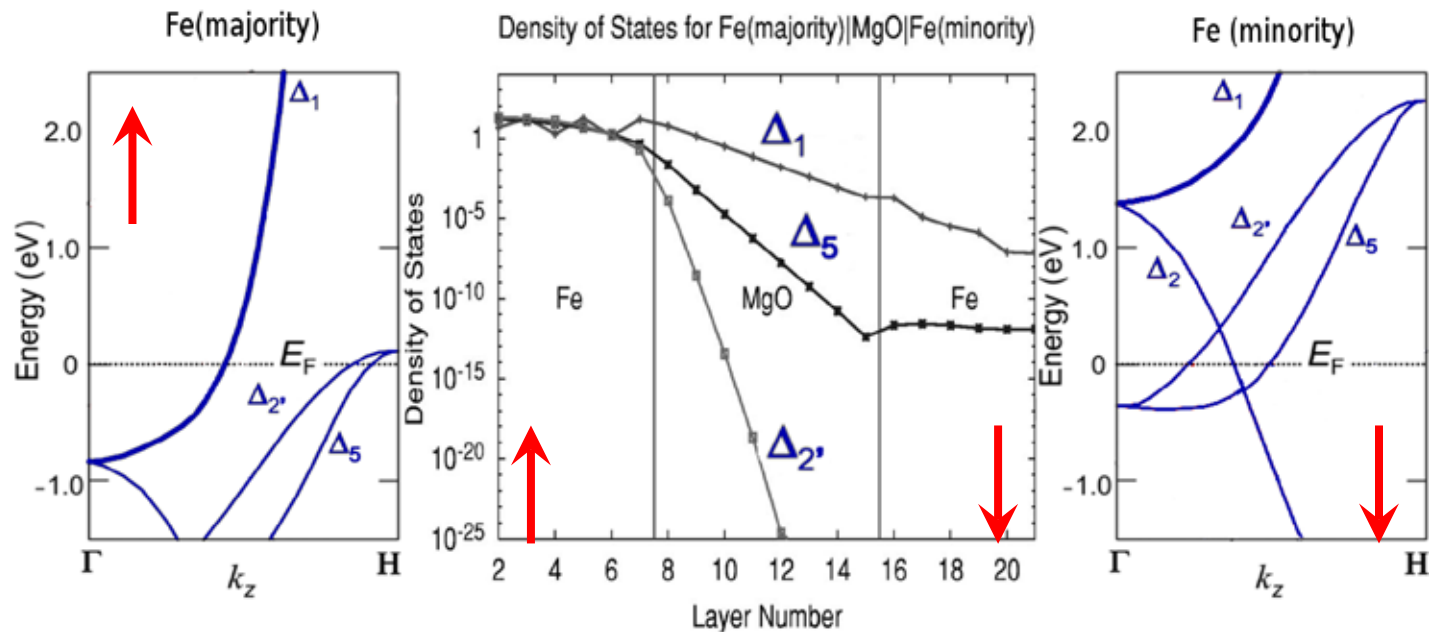


- Transmission probability is the same for different electronic bands

- Transmission probability changes for different electronic bands

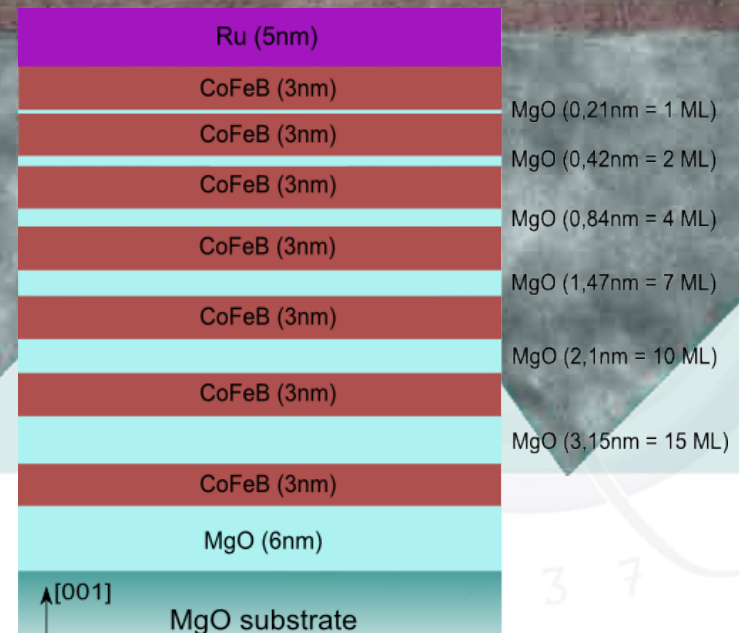
Giant tunneling magnetoresistance

Fe|MgO|Fe coherent tunneling



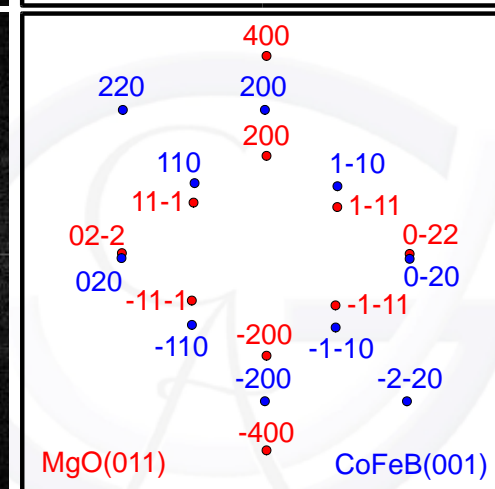
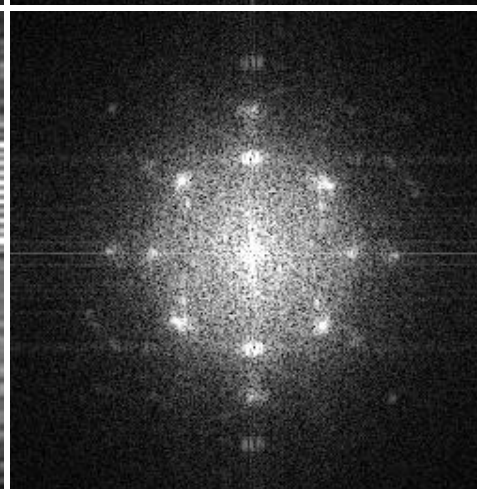
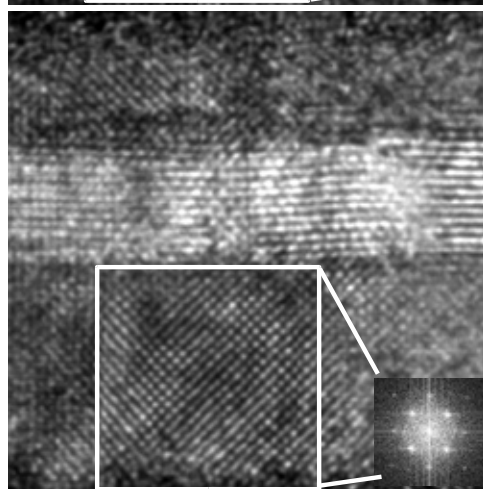
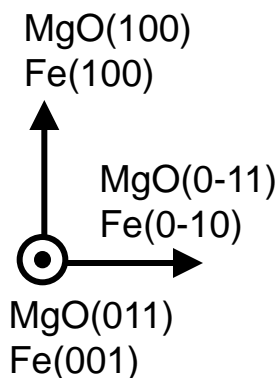
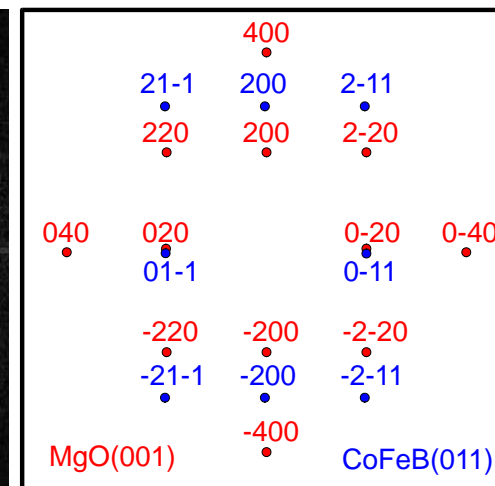
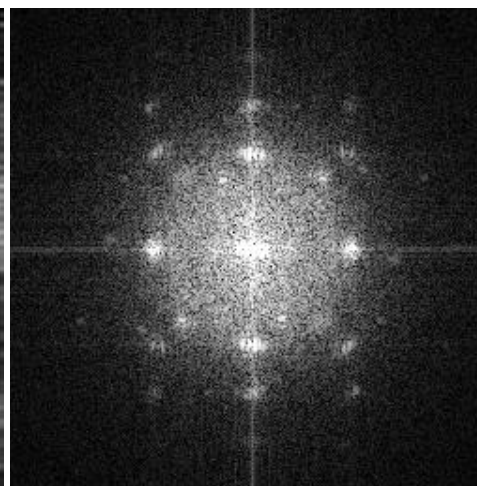
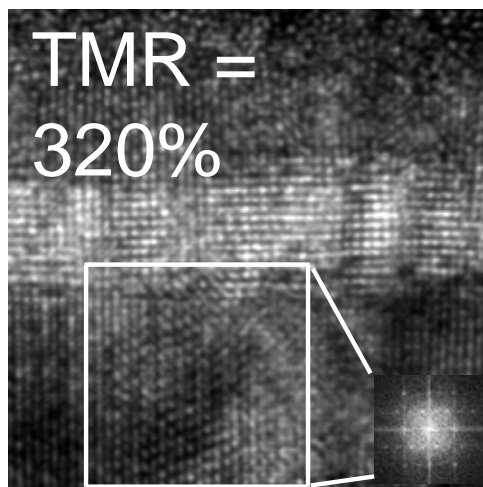
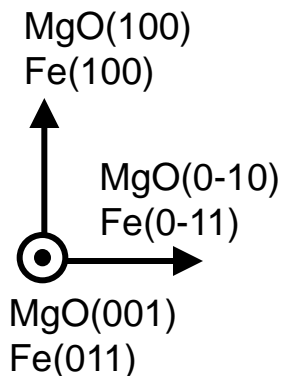
	Fe MgO Fe	Co MgO Co	FeCo MgO FeCo
Heiliger <i>et al.</i>	6000-8800%	900-2000%	
Mathon, Umerski	1200%		
Butler <i>et al.</i>	6000%	13000%	34000%

Pt



How thin can we get?

Atomic structure – columnar growth

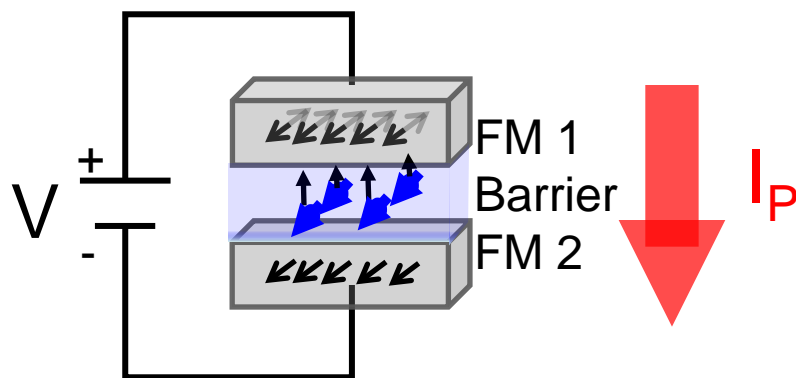


Sample annealed 400°C

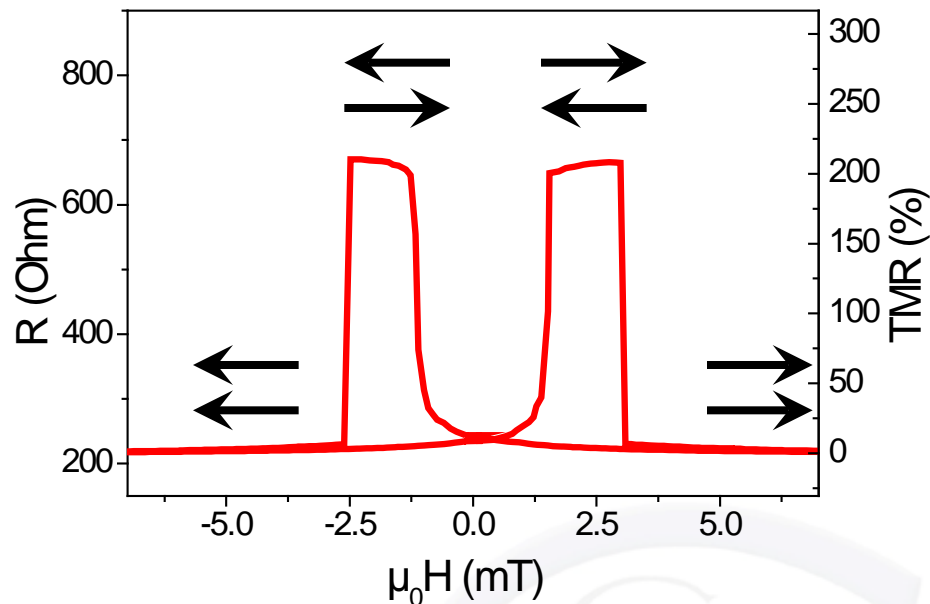
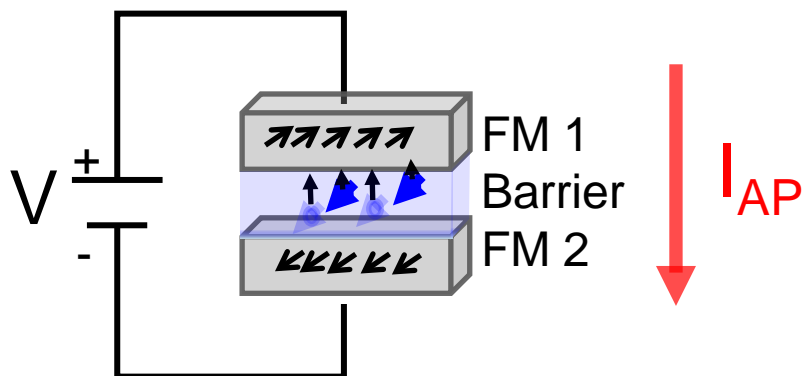
*In collaboration with: M. Seibt U Göttingen
A. Thomas, G. Reiss U Bielefeld*

Giant tunneling magnetoresistance

Parallel magnetization



Antiparallel magnetization



CoFeB/ MgO/ CoFeB junctions are half metallic with highest TMR (~600% at RT)

$$\text{TMR} = \frac{R_{AP} - R_P}{R_P}$$

Appl. Phys. Lett. **95**, 232119 (2009)

J. Appl. Phys. **105**, 073701 (2009)

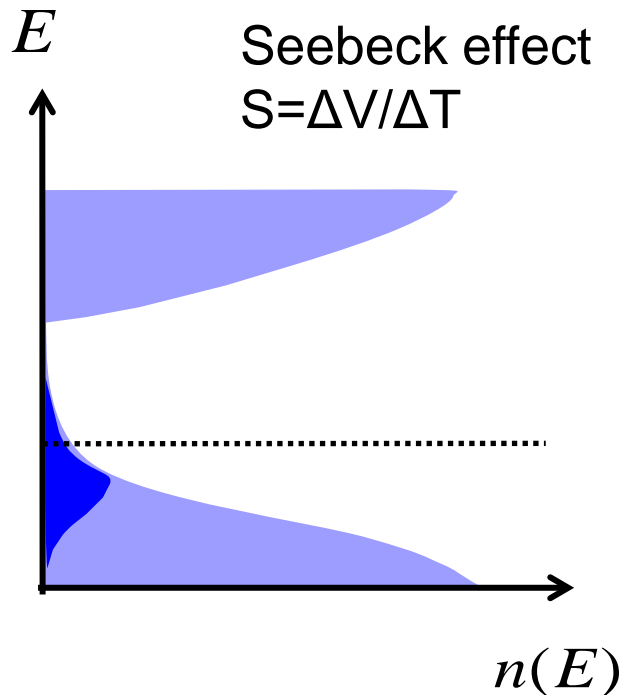
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Magneto-Seebeck effect

Semiconductor



Semiconductors have a large Seebeck effect

Origin is the

- Large asymmetry of the electrons at around the Fermi energy

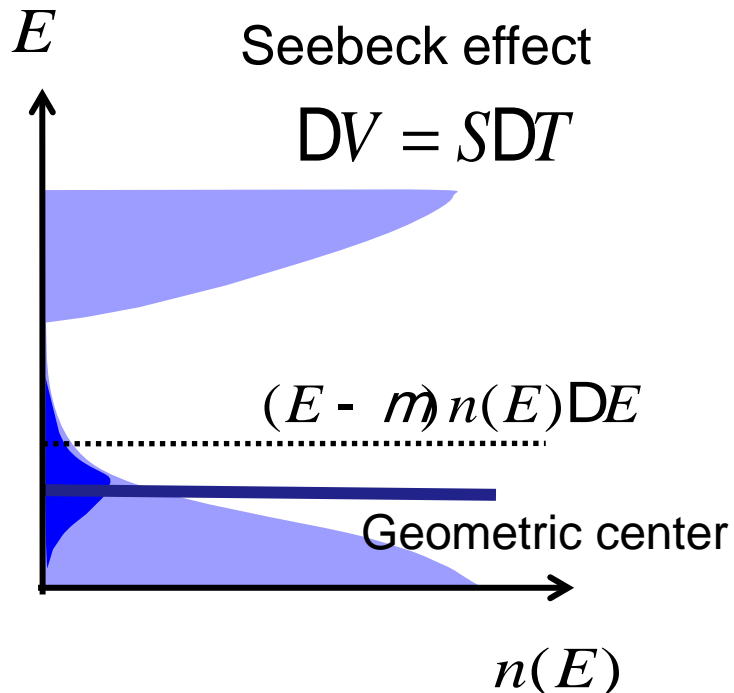
Conduction

- Determined by the density of states $n(E)$

$$g = \frac{e^2}{h} \int T(E) (-\partial_E f(E, \mu, T)) dE$$

Magneto-Seebeck effect

Semiconductor



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Conduction

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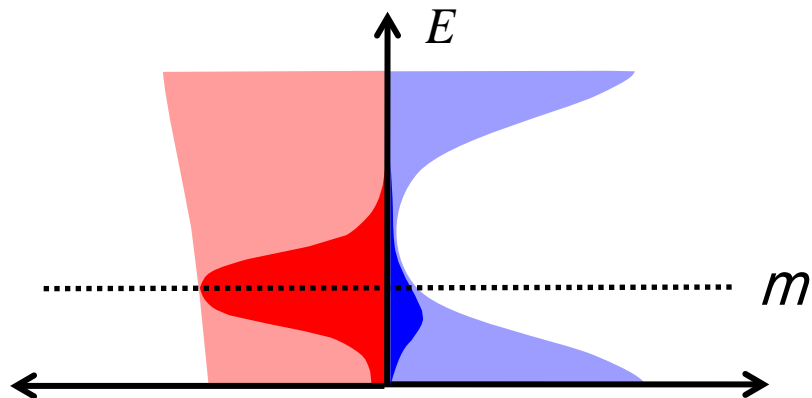
Seebeck coefficient S

- Determined by density of states
- weighed by $(E - \mu)$
- times derivative $\frac{df(E)}{dE}$

$$S = - \frac{\int T(E)(E - \mu)(-\partial_E f(E, \mu, T))dE}{eT \int T(E)(-\partial_E f(E, \mu, T))dE}$$

Magneto-Seebeck effect

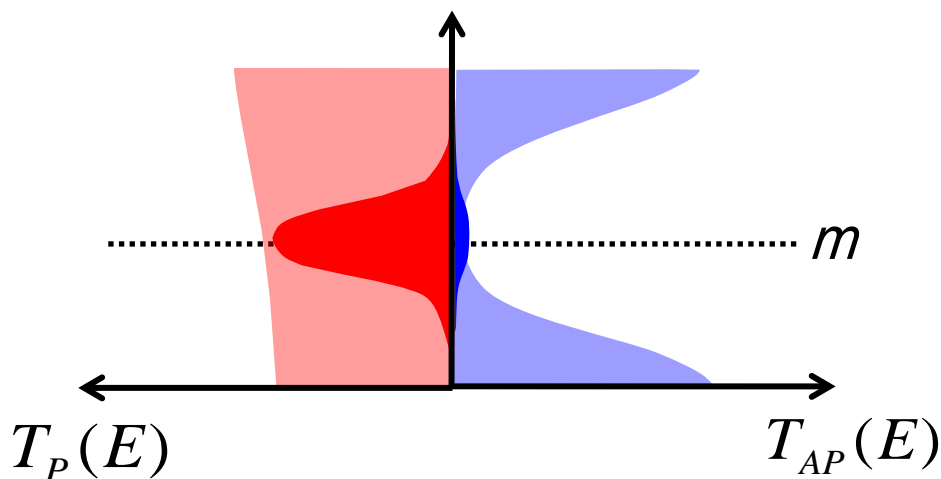
Tunnel junction



For tunnel junctions:

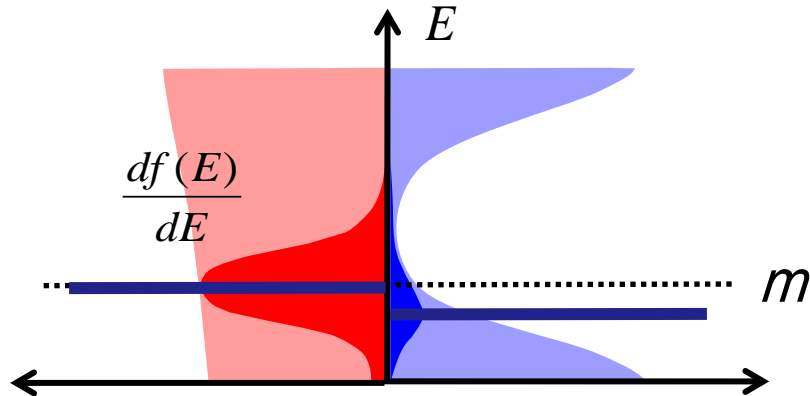
Conduction

- Determined by the transmission $T(E)$
- High TMR



Magneto-Seebeck effect

Tunnel junction



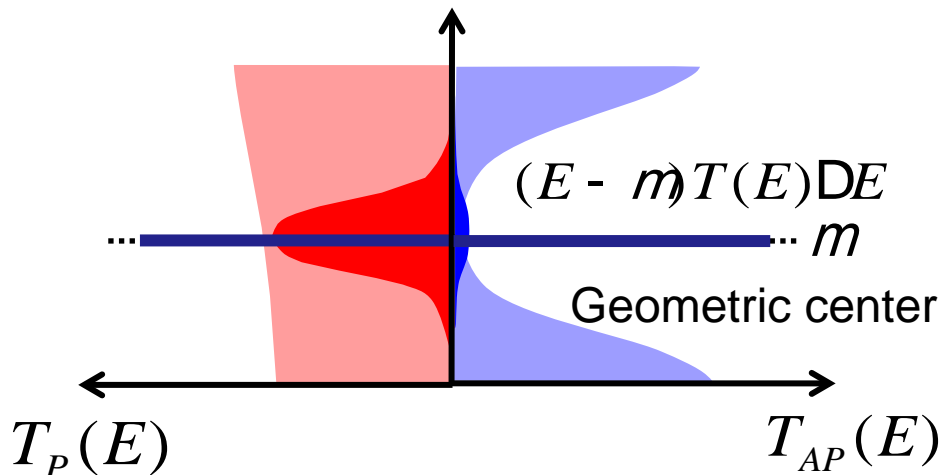
For tunnel junctions:

Conduction

- Determined by the transmission $T(E)$

Seebeck coefficient

- Determined transmission $T(E)$
- weighed by $(E - m)$
- times derivative $\frac{df(E)}{dE}$



Definition of the magneto-Seebeck effect

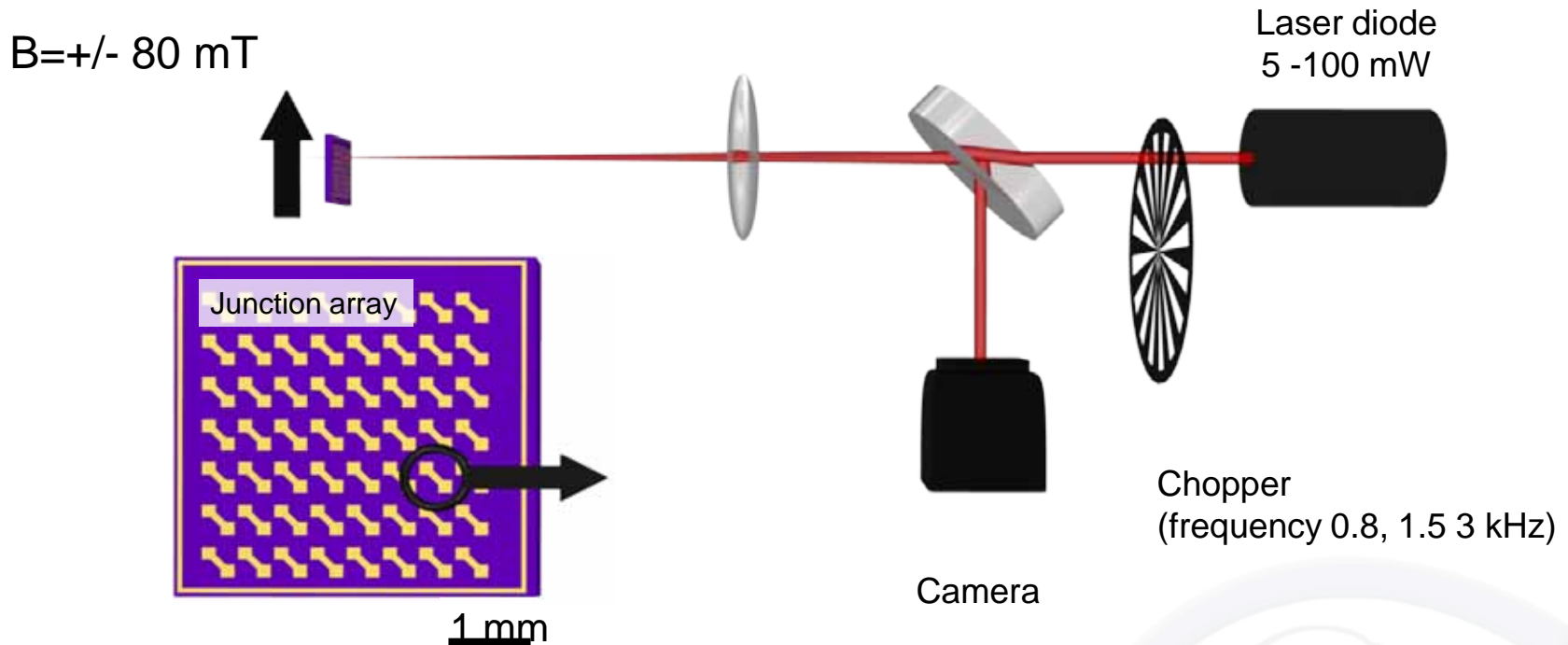
$$S_{MS} = \frac{S_P - S_{AP}}{\min(S_P, S_{AP})}$$

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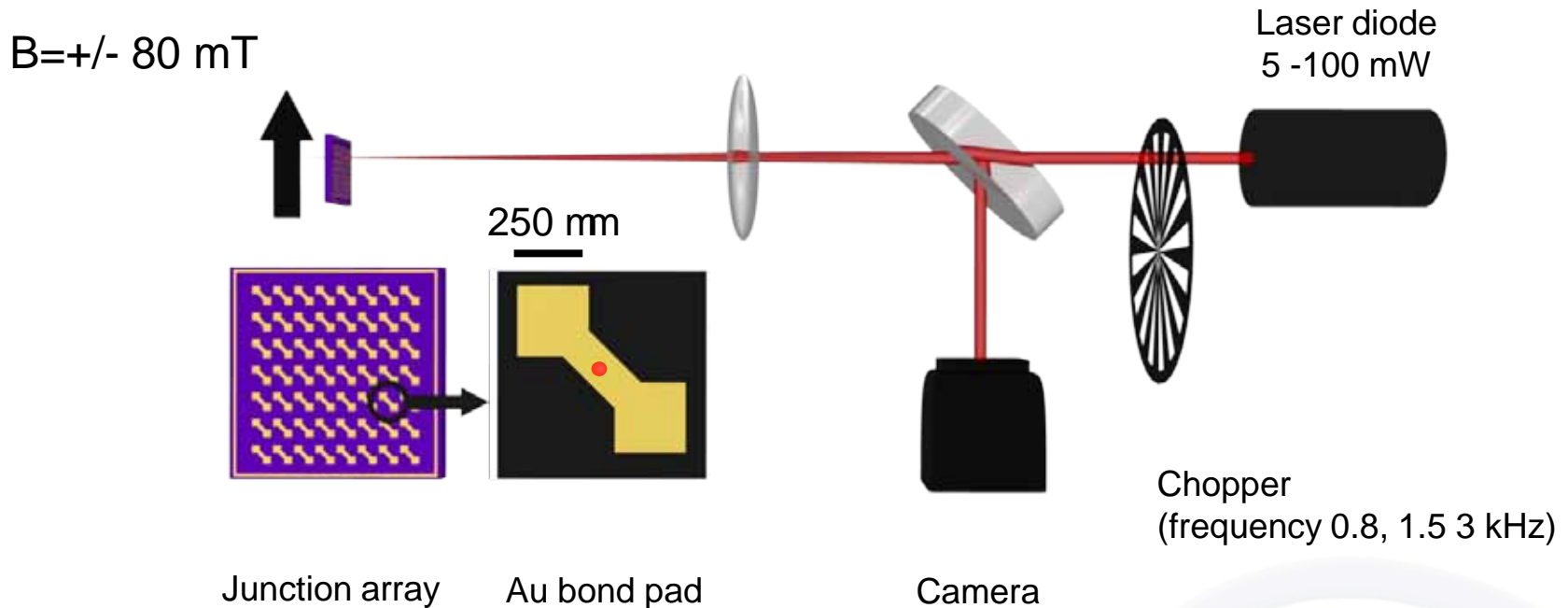


Experimental setup



- Toptica stabilized laser diode (784 nm)
- Most experiments: 30 mW laser power
- Modulation 800 Hz, 1.5 kHz, and 3 kHz

Experimental setup

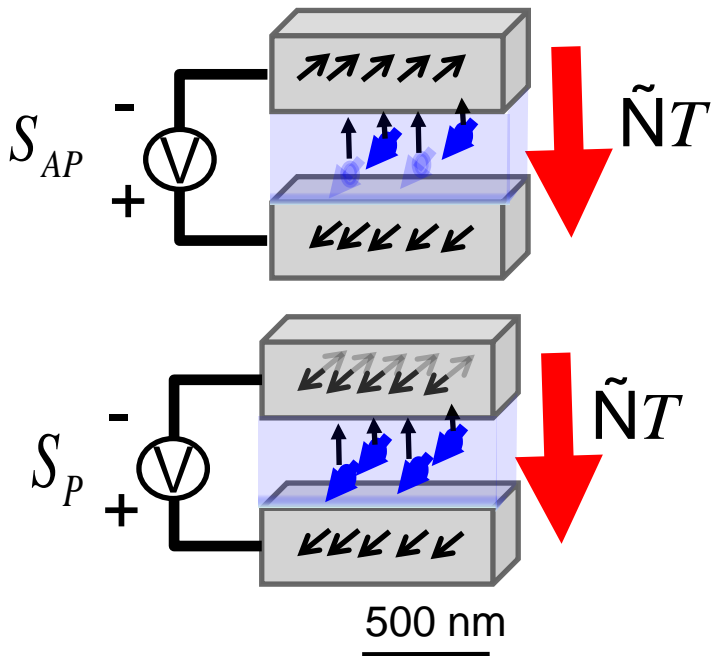


- Focus 15-20 μm diameter
- High input impedance (100 $\text{G}\Omega$) (LT1113 Linear Technology)
- Resistance change $< 1 \text{ nV}$

Experimental setup

$B = \pm 80 \text{ mT}$

Laser diode
5 -50 mW



Seebeck effect:

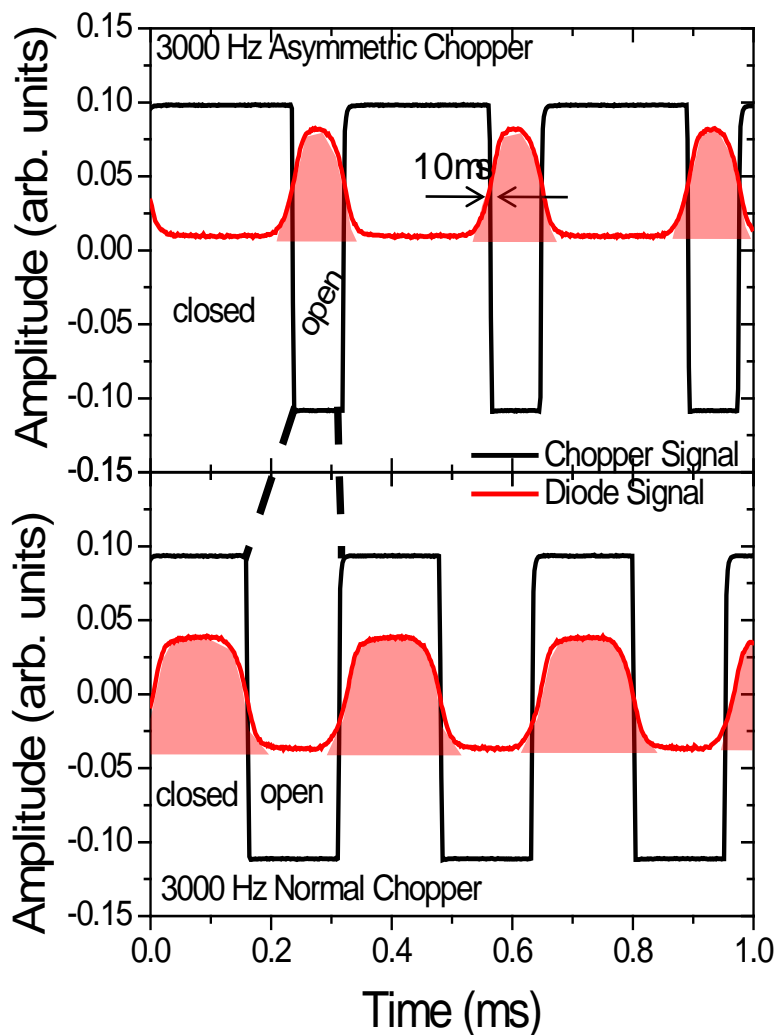
$$DV_{P,AP} = S_{P,AP} DT$$

Magneto -Seebeck effect:

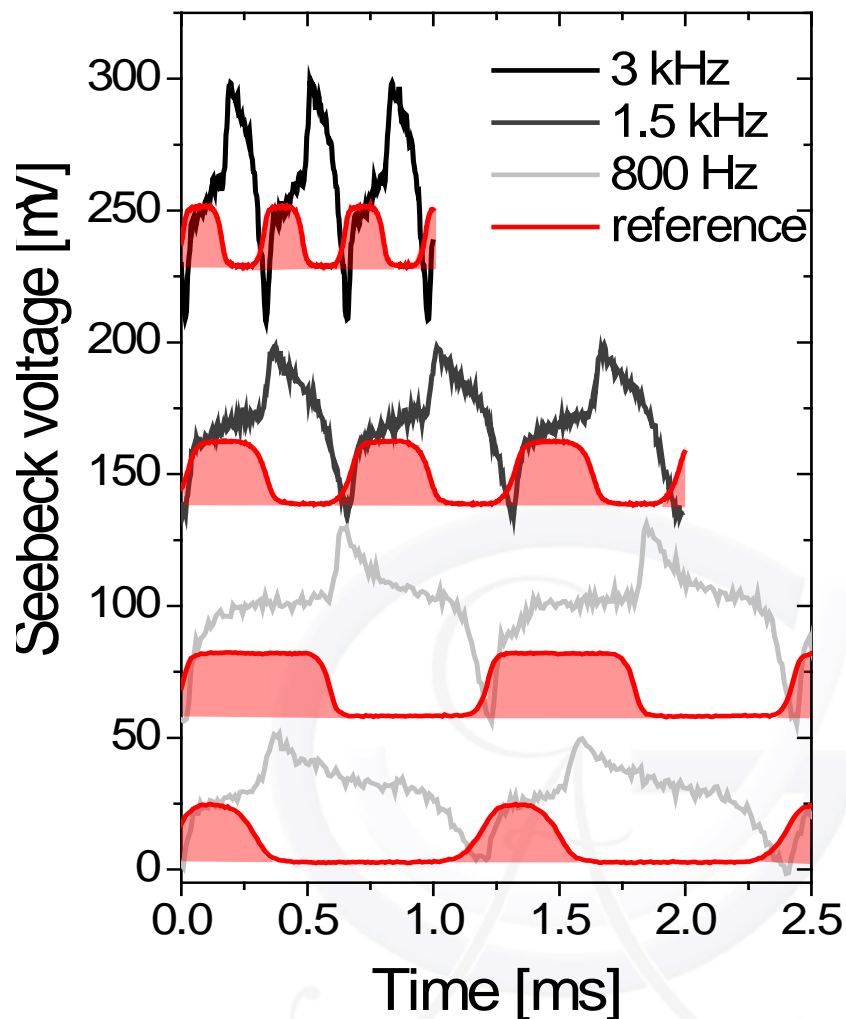
$$S_{MS} = \frac{S_P - S_{AP}}{\min(S_P, S_{AP})}$$

Experimental setup

Modulation chopper and laser intensity



Seebeck voltage

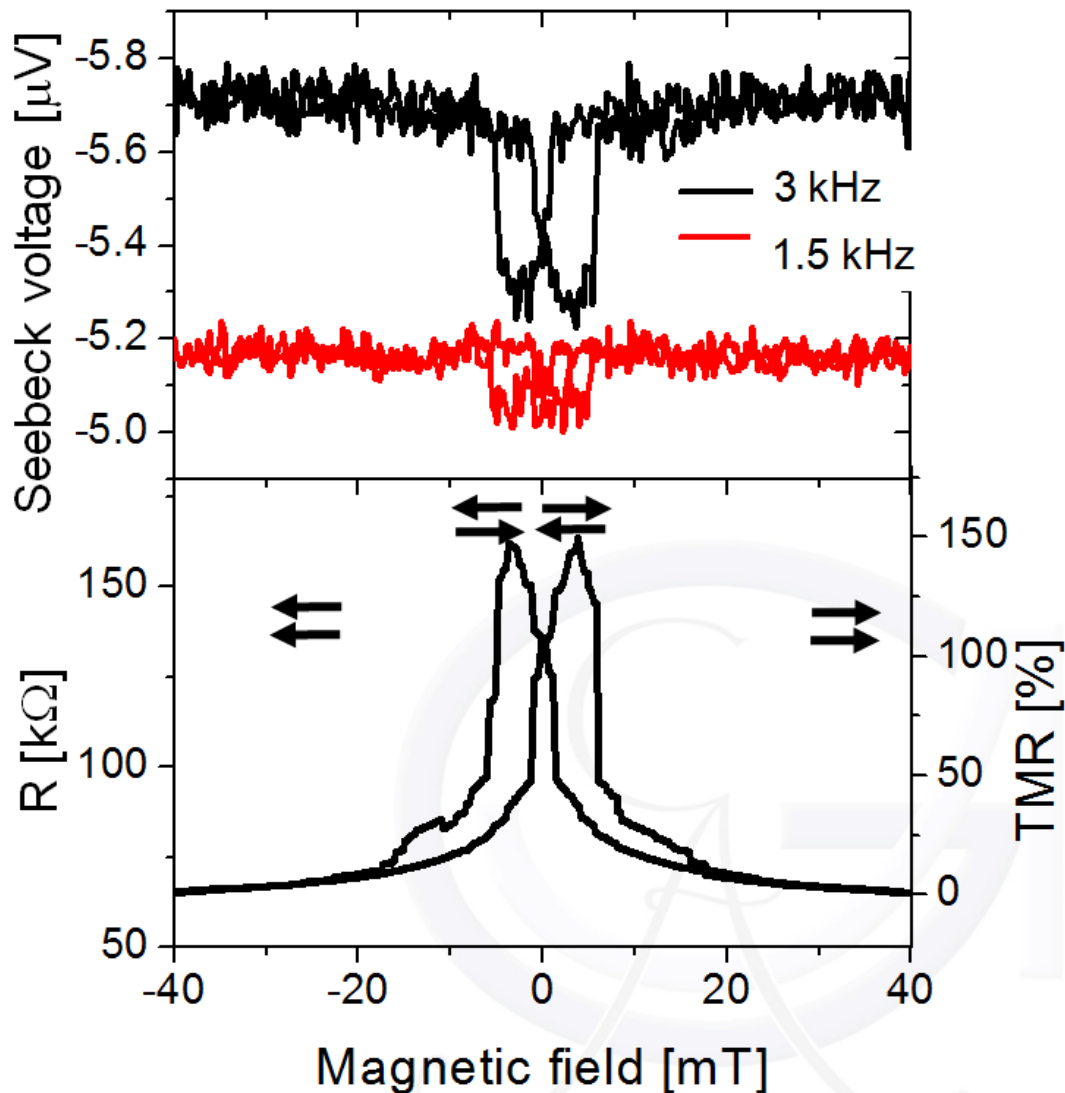
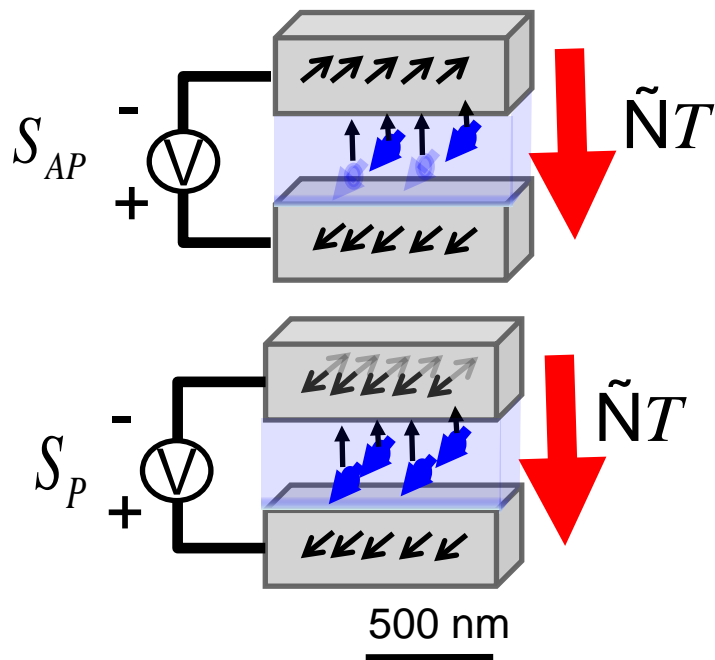


Magneto-Seebeck effect

Magneto-Seebeck effect: -8.8%

Seebeck voltage 0.45 mV, DS= -8.7 mV/K

$$S_{MS} = \frac{S_P - S_{AP}}{\min(S_P, S_{AP})}$$



Outline

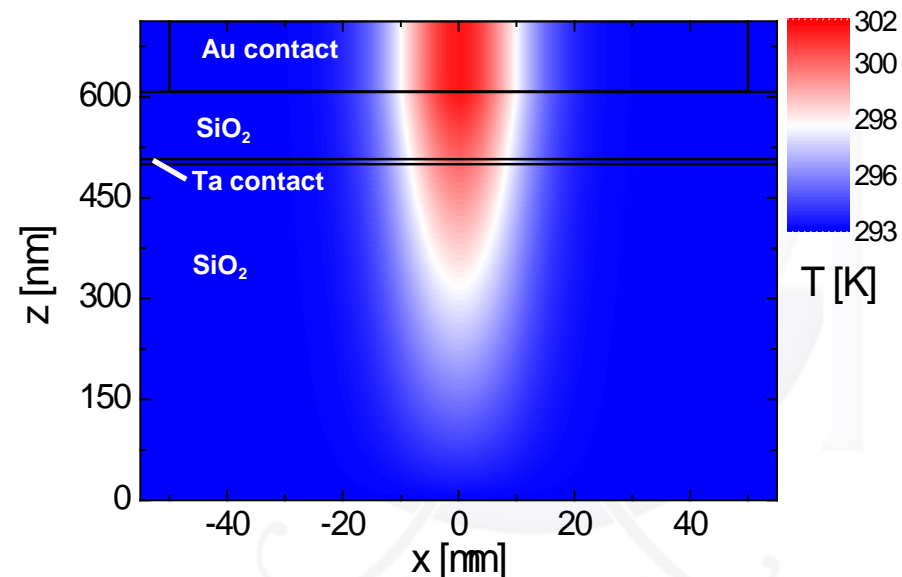
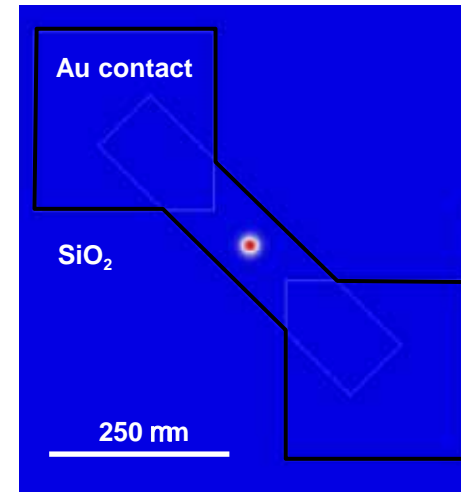
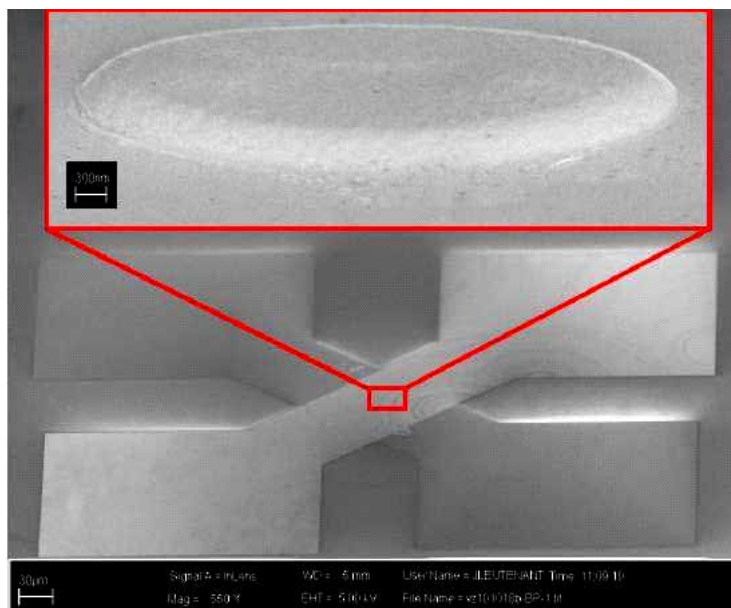
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COMSOL finite element modeling

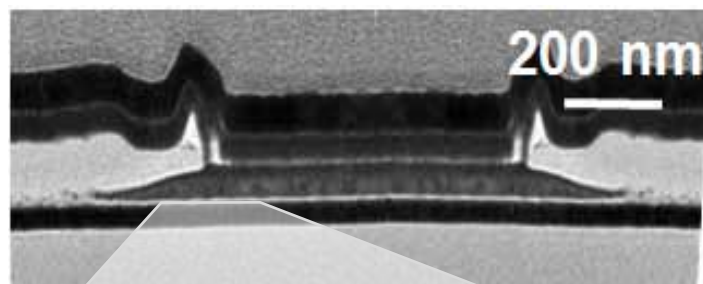
- COMSOL uses finite elements methods
- Solving of heat conduction equation

$$\rho c_p \frac{\partial T}{\partial t} = \nabla \cdot (k \nabla T) + Q$$

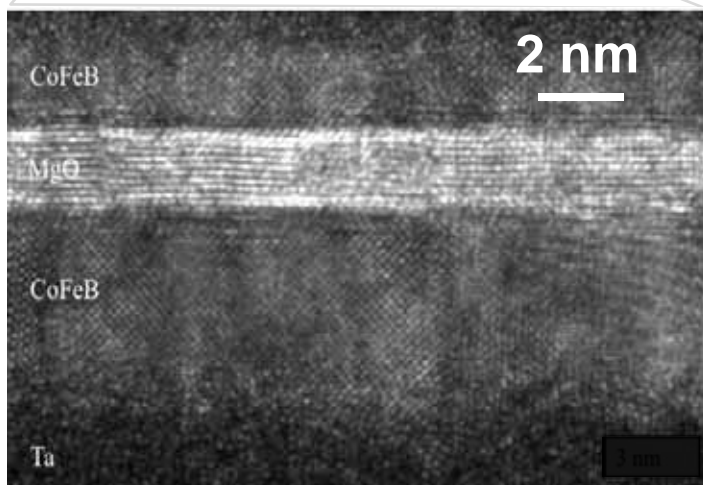


COMSOL finite element modeling

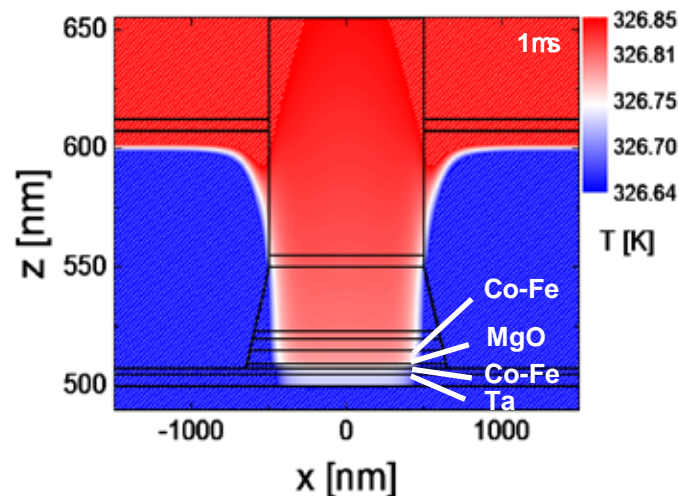
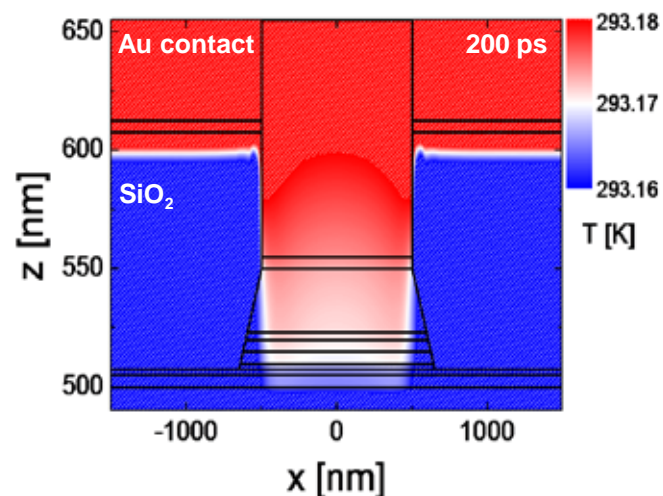
Device structure by HRTEM



x 40



Temperature gradients: 1 to 50 mK



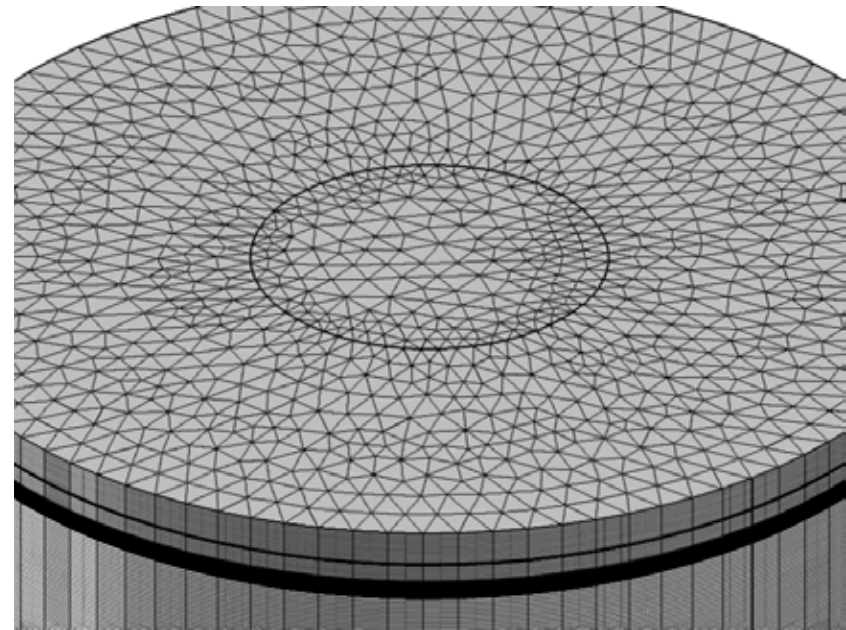
COMSOL finite element modeling

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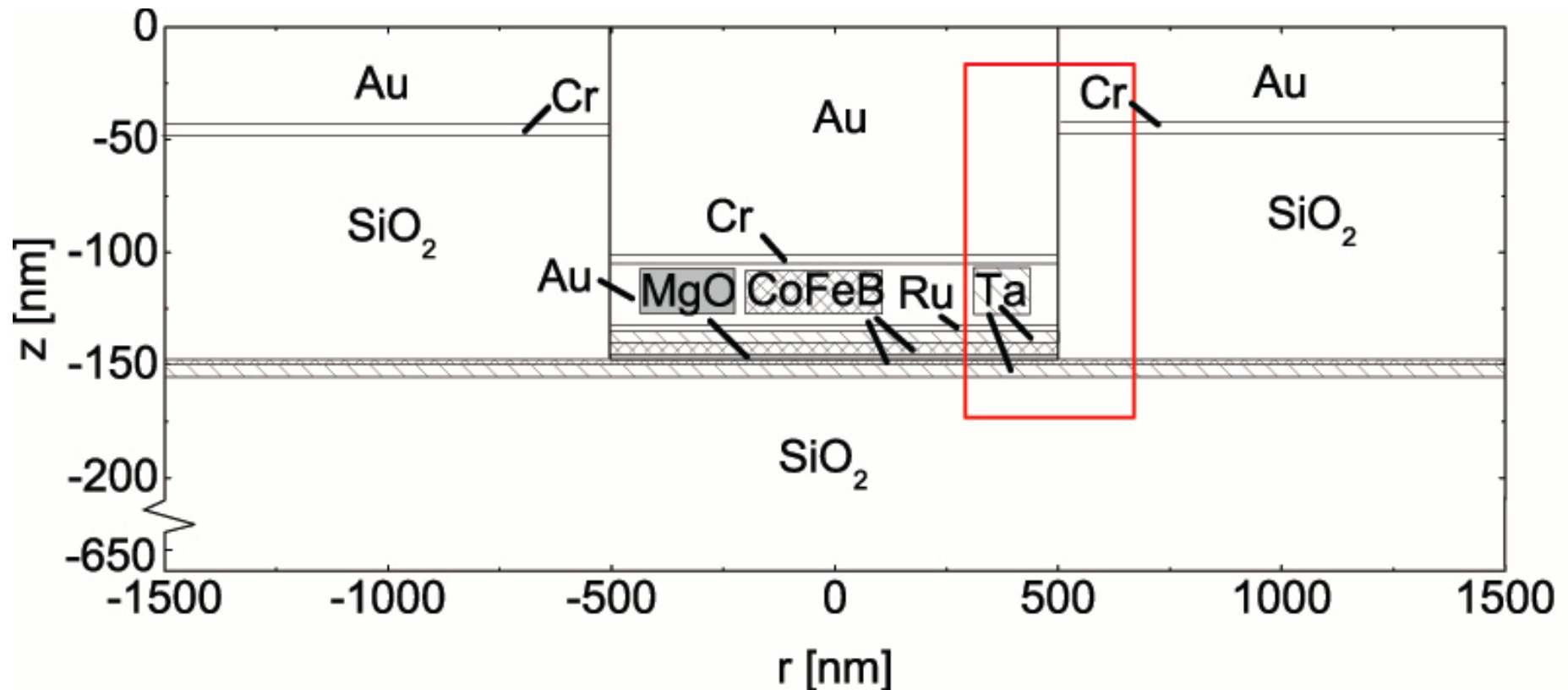
$$\rho c_p \frac{\partial T}{\partial t} = \nabla \cdot (k \nabla T) + Q$$

- 3d or 2d cylindrical model

Material	κ [W/(m·K)]
Ta	57
Ru	117
Au	320
Cr	94
MgO	4 (48)
SiO ₂	1.4
Co ₂₀ Fe ₆₀ B ₂₀	87



COMSOL finite element modeling

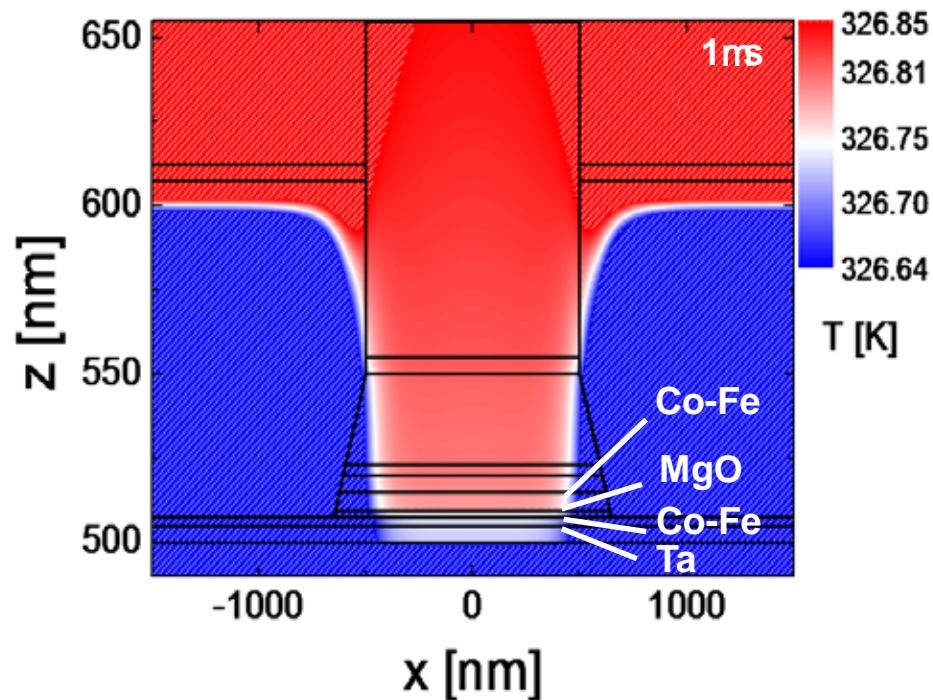
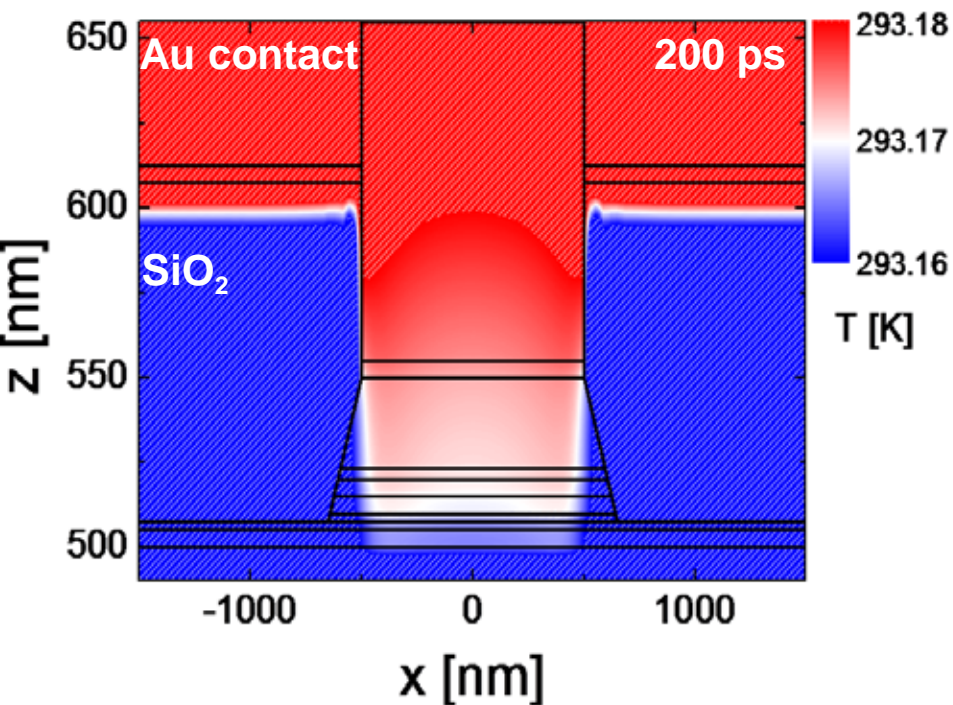


COMSOL finite element modeling

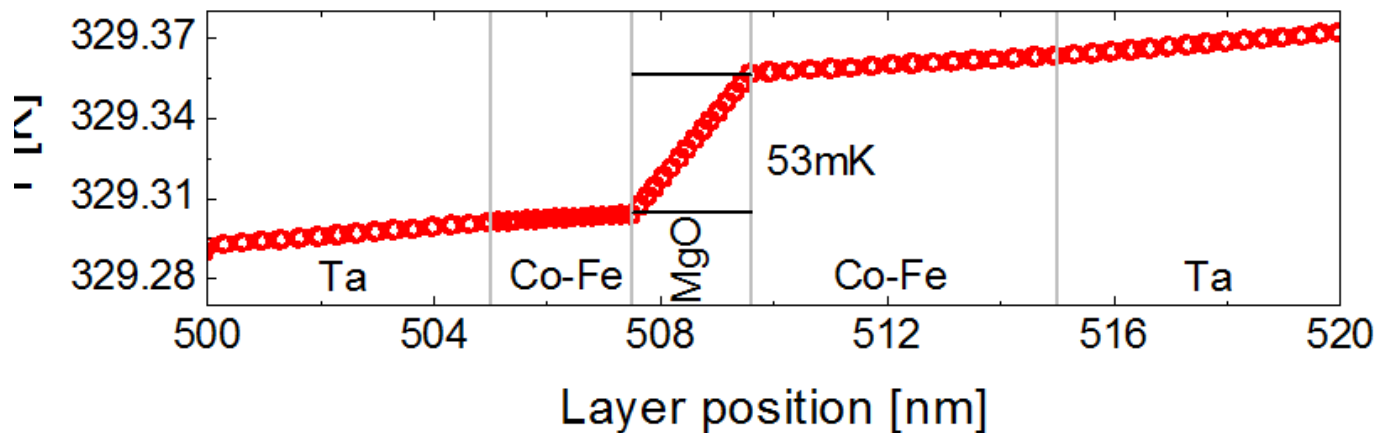
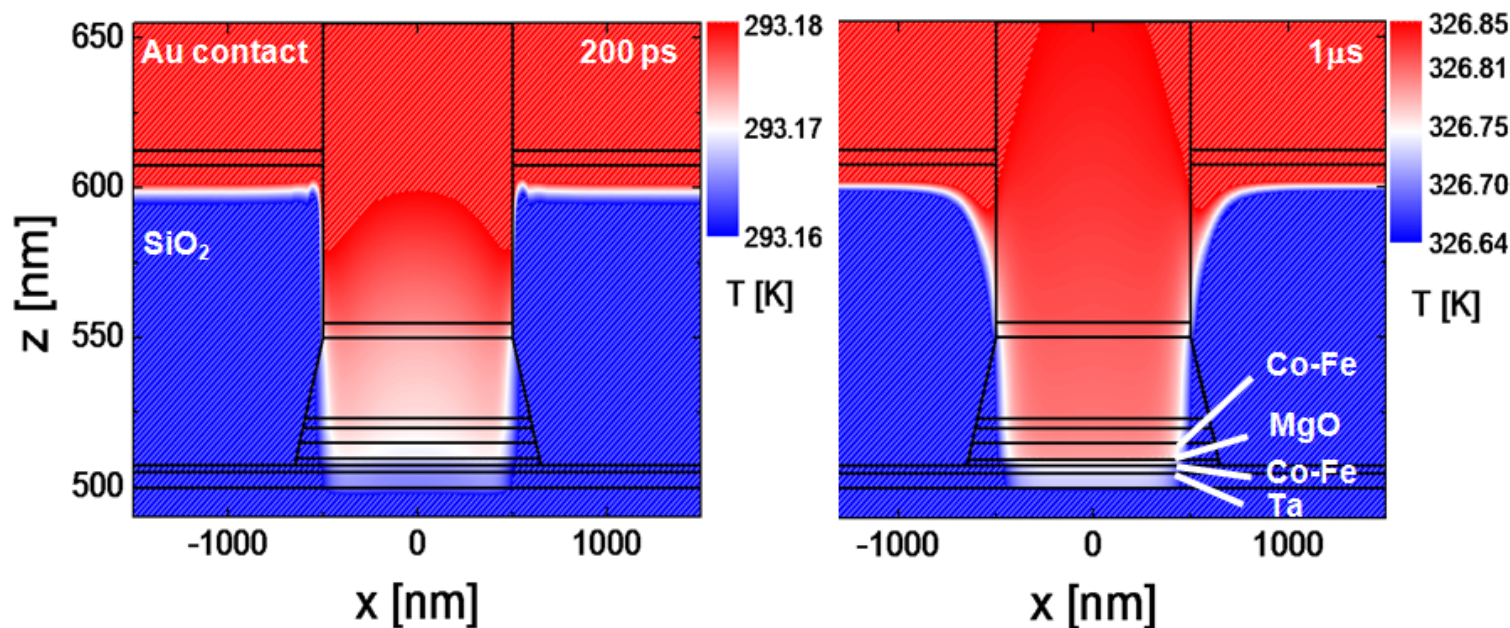
Cross section of the finite element model

Temperature gradients: 1 to 50 mK

$$S = DV/DT$$



COMSOL finite element modeling

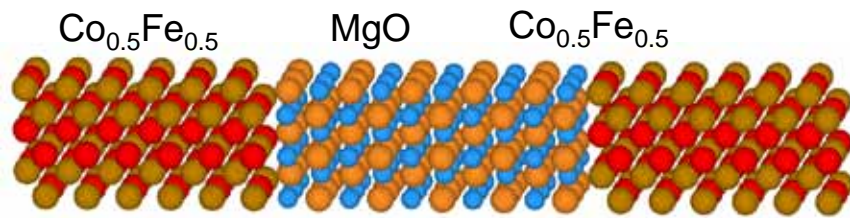


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Magneto-Seebeck effect



For tunnel junctions:

Conduction

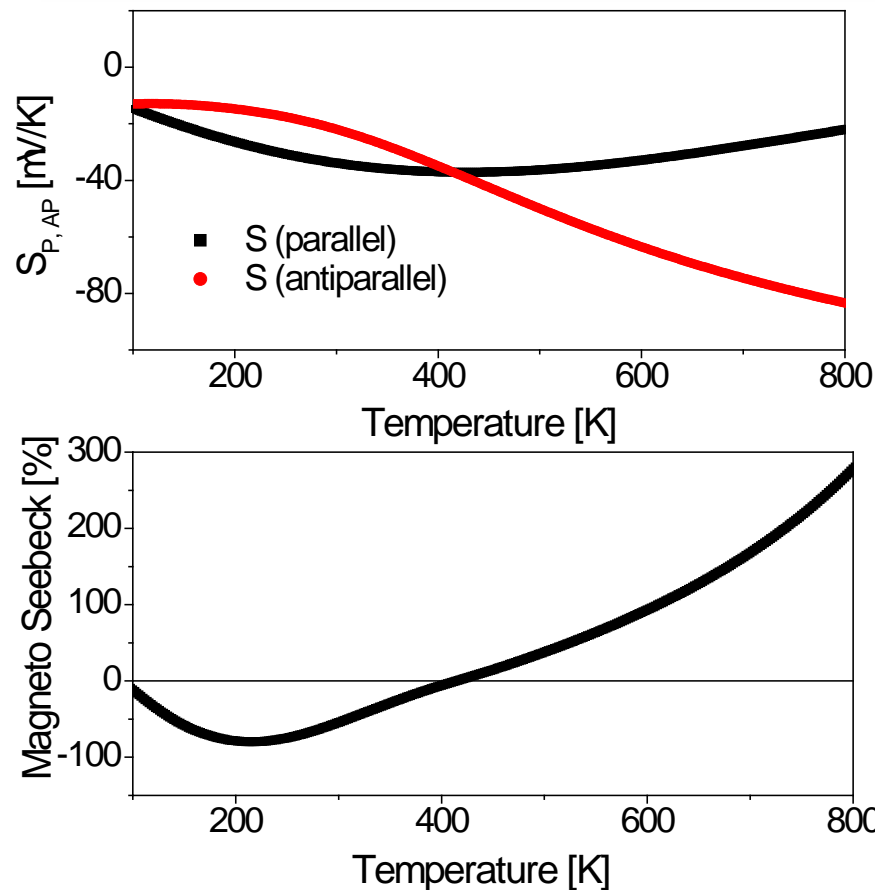
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Seebeck coefficient

$$S = - \frac{\int T(E) (E - \mu) (-\partial_E f(E, \mu, T)) dE}{eT \int T(E) (-\partial_E f(E, \mu, T)) dE}$$

Definition of the magneto-Seebeck effect

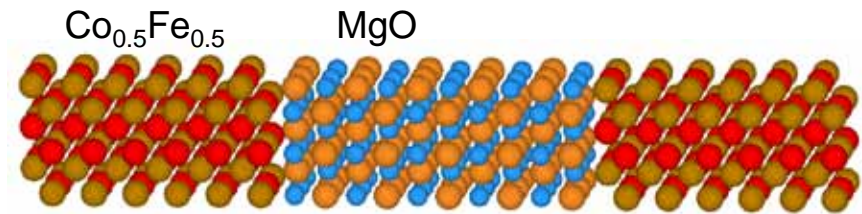
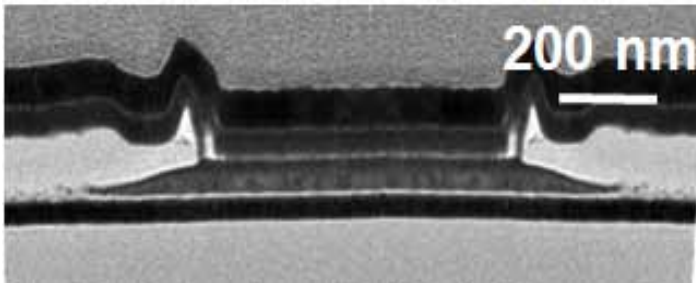
$$S_{MS} = \frac{S_P - S_{AP}}{\min(S_P, S_{AP})}$$



Magneto-Seebeck effect

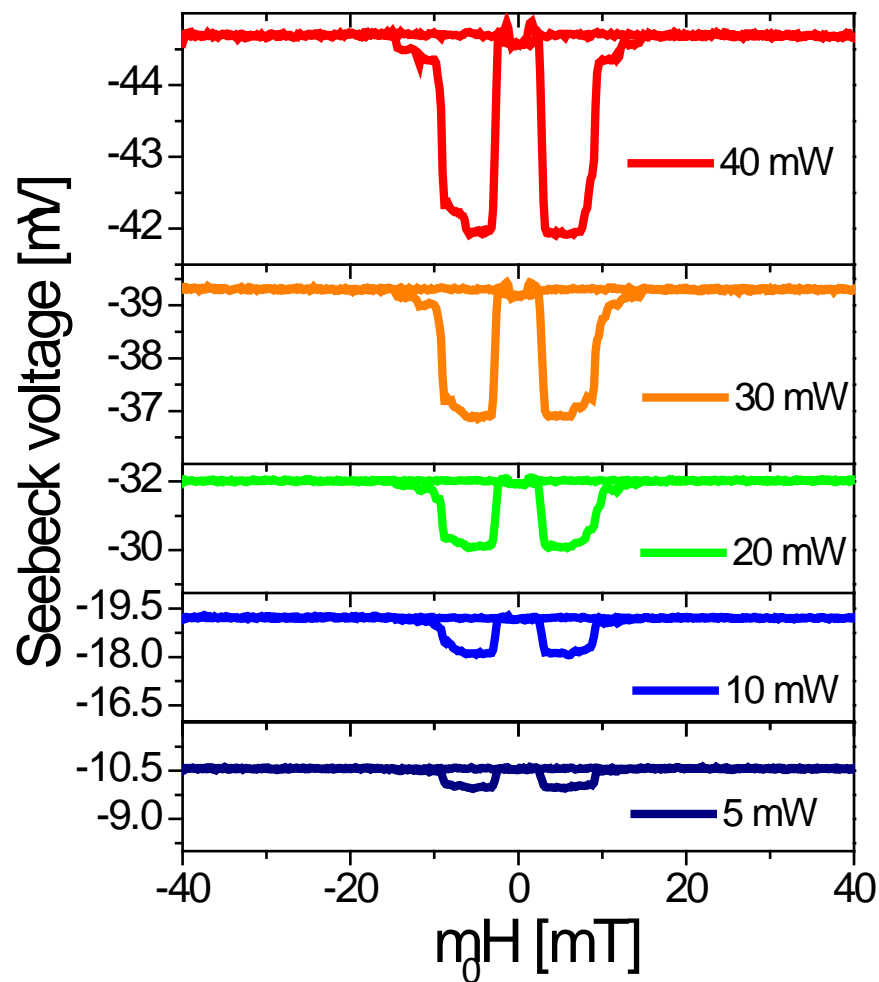
Device structure by HRTEM

Seebeck voltage 0.45 mV, DS= -8.7 mV/K



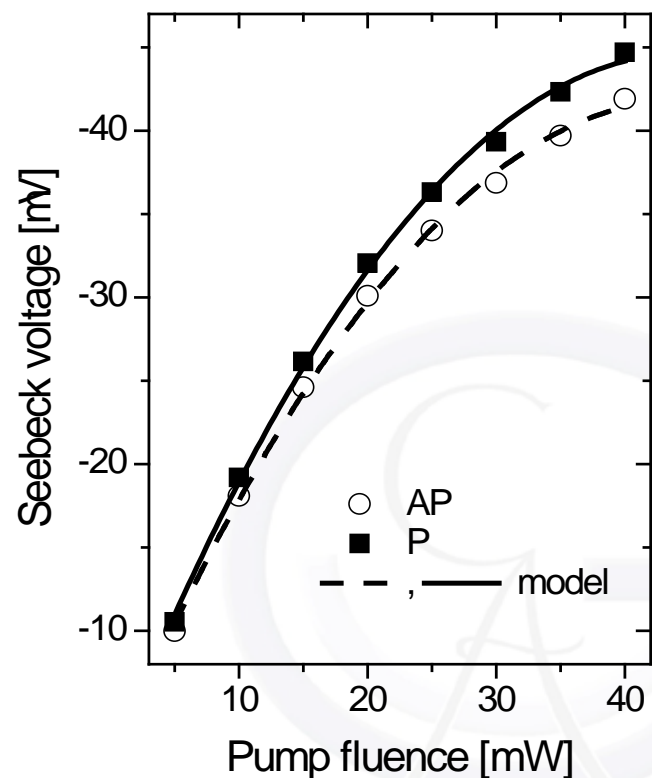
	S_P [$\mu\text{V/K}$]	S_{AP} [$\mu\text{V/K}$]	$S_P - S_{AP}$ [$\mu\text{V/K}$]	S_{MS} [%]
CoFe	-19.7	-32.4	12.7	64.1
FeCo	45.9	-50.0	95.9	209.0
CFFC	9.4	-44.6	54.0	573.2
Co _{0.5} Fe _{0.5}	-34.0	-21.9	-12.1	-55.2
Experimental value	-107.9 (-1300)	-99.2 (-1195)	-8.7 (-105)	-8.8 (-8.8)

Magneto-Seebeck effect

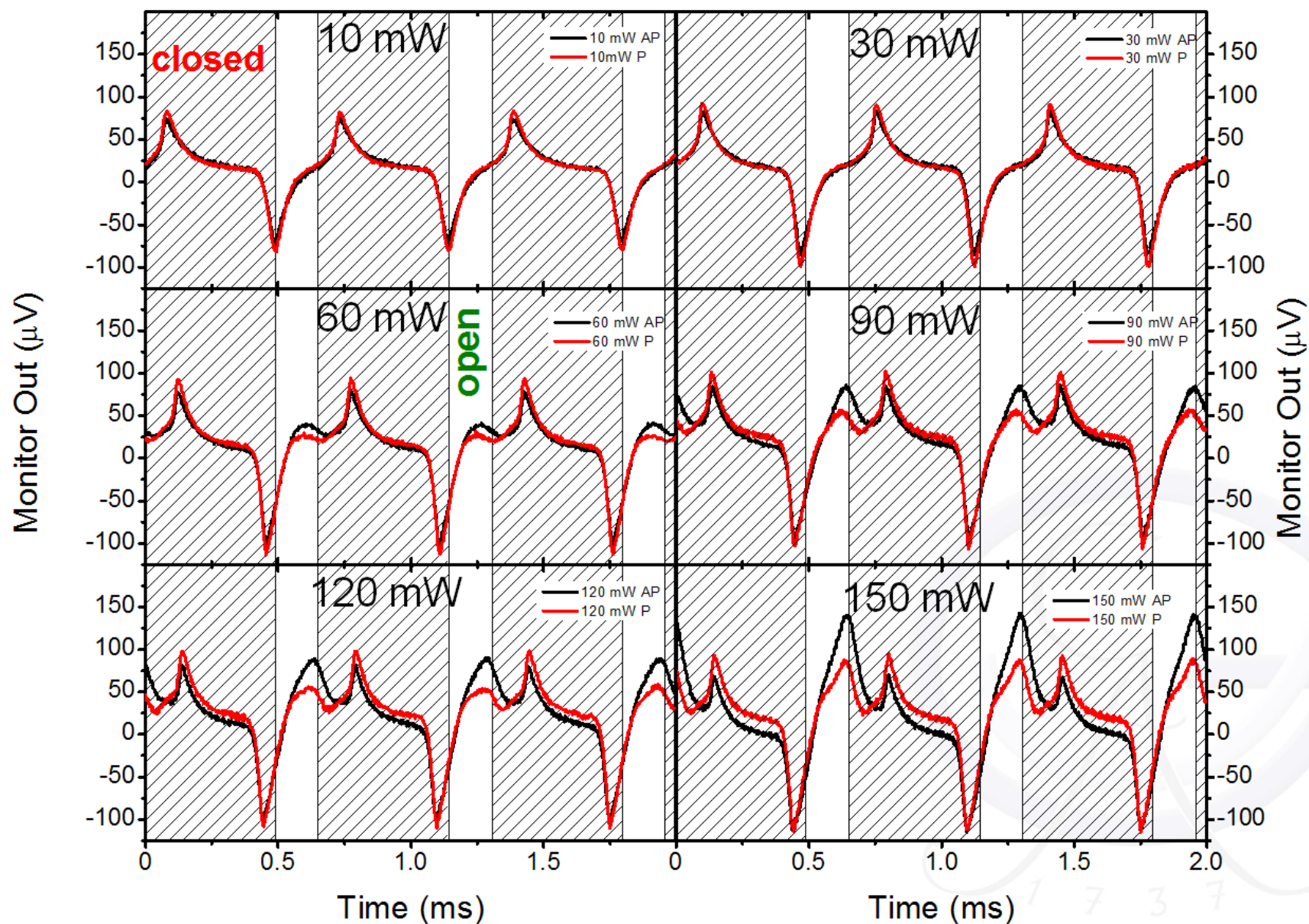


Higher T and gradient expected for higher laser powers

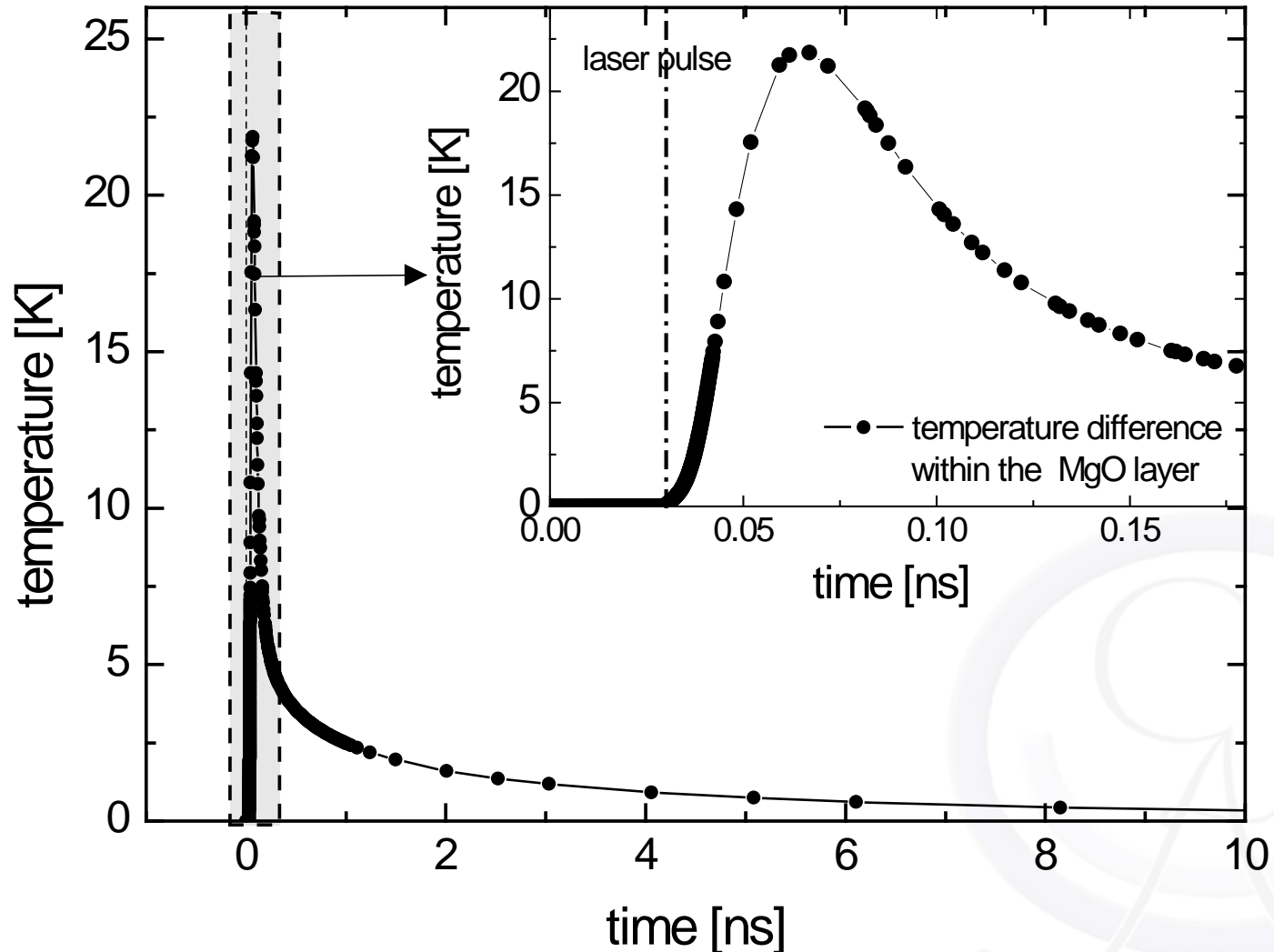
- nonlinear behavior $DV = S(T)DT$



High fluence data: femtosecond laser



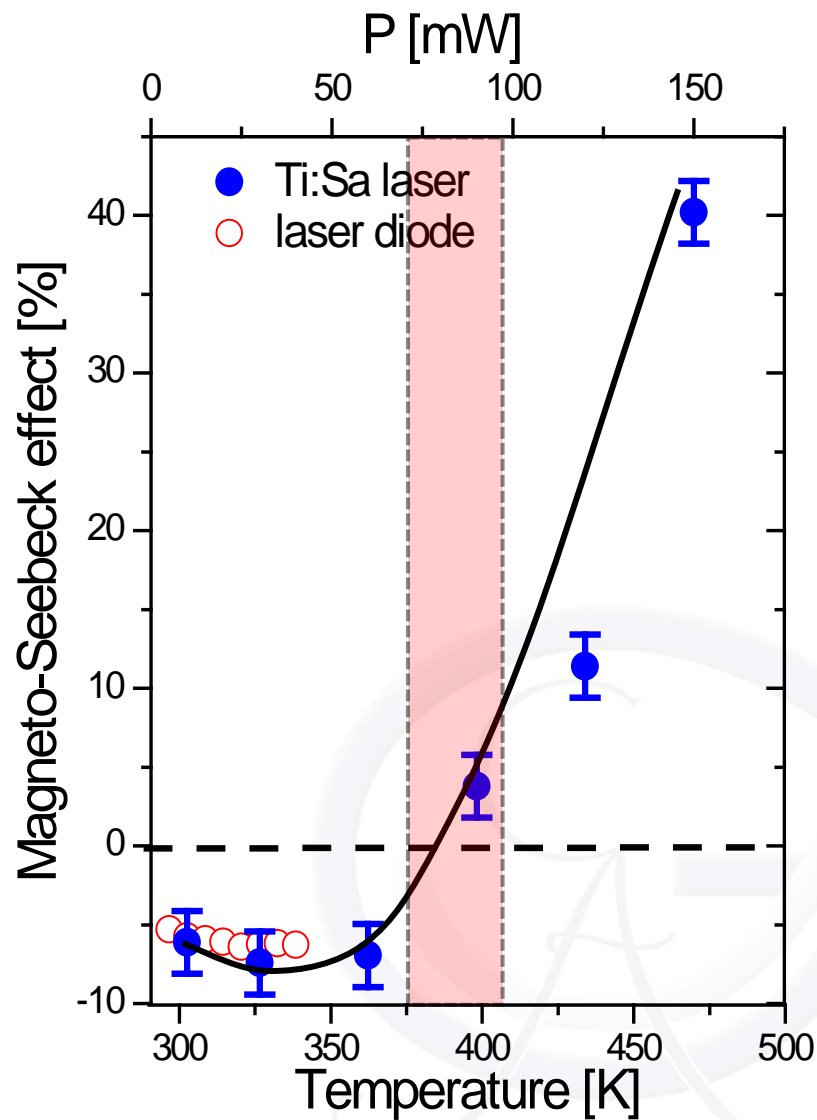
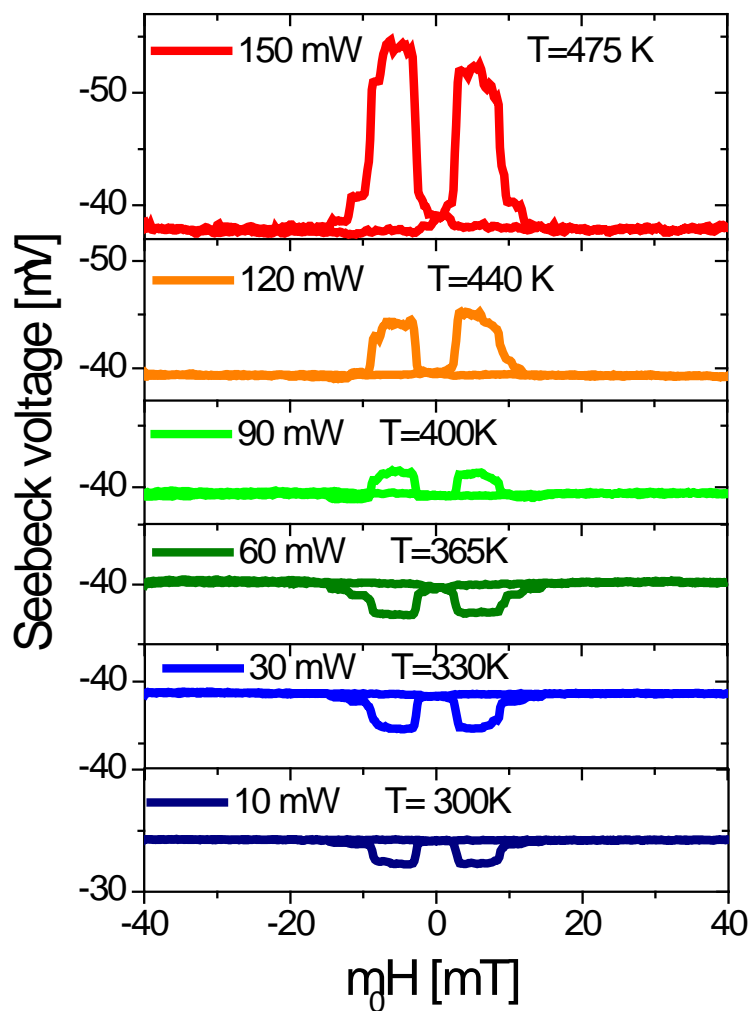
High fluence data: femtosecond laser



- Large temperature gradients are achievable: 10K per nanometer

Magneto-Seebeck effect

Sign change as predicted:



Summary

- Magneto-Seebeck experiment:
 - Experimental verification
 - Simulations of the temperature gradients
 - Switching of Seebeck coefficients demonstrated
- Ab initio calculations
 - Typical features are reproduced by the experiment



Increasing temporal resolution

Seebeck voltage autocorrelation:

- Femtosecond laser excitation (40 fs temporal resolution)
- Delay t in between the pulses
- Probes non-linearity of the Seebeck voltage
- ~80 ps time scale is the expected timescale when the maximum temperature difference is reached (from simulation)

